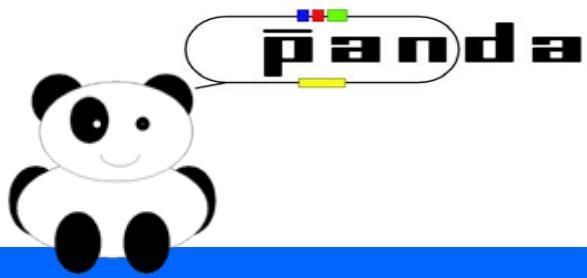


# L'esperimento PANDA ed il rivelatore a pixel per il microvertice



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from PANDA collaboration

Scuola Nazionale "Rivelatori ed Elettronica per Fisica delle Alte Energie, Astrofisica, Applicazioni Spaziali e Fisica Medica", 20-24 aprile 2009, LNL



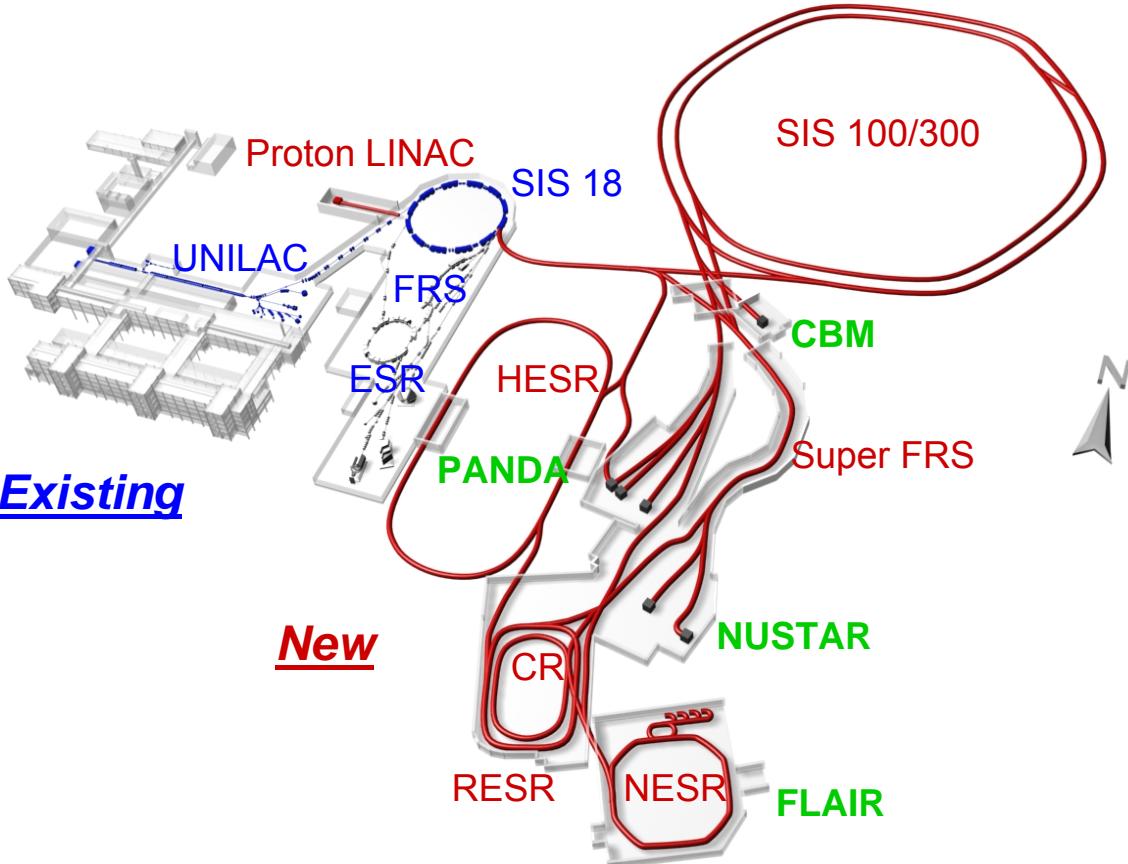
# Overview

- Introduction to FAIR and HESR
- The PANDA experiment
- The Micro Vertex Detector
- Prototypes for the Custom Pixel Detector

# The future Facility FAIR in Darmstadt



## Facility for Antiproton and Ion Research



### Antiproton production

- Proton LINAC 50 MeV
- Accelerate p in SIS18 / 100
- Produce antiproton on Cu target
- Collect in CR, cool in RESR

### Primary beams

- $10^{12}/\text{s}$ ;  $1.5 \div 2 \text{ GeV/u}$ ;  $^{238}\text{U}^{28+}$
- Factor  $100 \div 1000$  over present intensity
- $2 \cdot 10^{13}/\text{s}$  30 GeV protons
- $10^{10}/\text{s}$   $^{238}\text{U}^{73+}$  up to 35 GeV/u
- 50 MeV new Proton LINAC

### Secondary beams

- Broad range of radioactive beams up to  $1.5 \div 2 \text{ GeV/u}$
- Intensity up to factor 10000 over present
- Antiprotons  $1.5 \div 15 \text{ GeV/c}$

### Storage and Cooler Rings

- $10^{11}$  stored and cooled  $0.8 \div 14.5 \text{ GeV}$  antiprotons

### Parallel operations

- Up to 4 different independent experiments

# HESR-High Energy Storage Ring

Circumference = 574 m

$P_{beam}$  = 1.5 ÷ 15 GeV/c

$N_{stored}$   $\leq 10^{11}$  antip

Internal thick Target =  $4 \cdot 10^{15}$  cm $^{-2}$

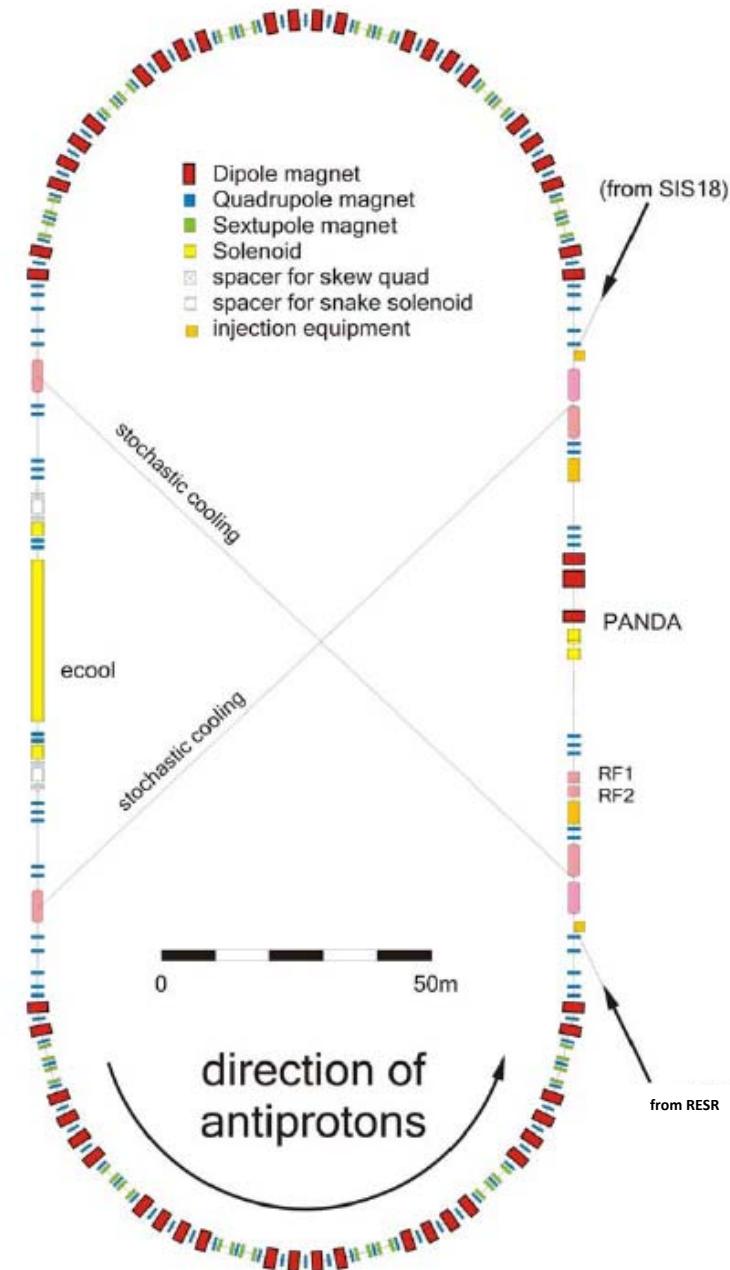
Beam lifetime > 30 min

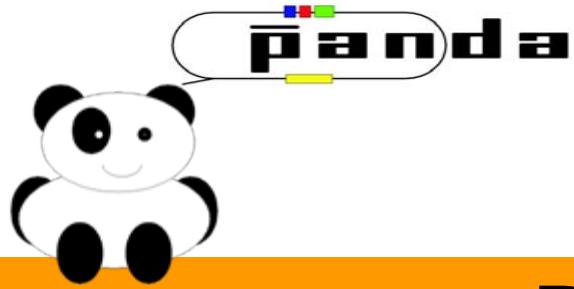
- **High resolution mode**

- $\delta p/p \sim 4 \cdot 10^{-5}$
- Momentum range = 1.5 ÷ 8.9 GeV/c
- Electron cooling  $\leq 8.9$  GeV/c
- Antiprotons number =  $10^{10}$
- Peak luminosity =  $2 \cdot 10^{31}$  cm $^{-2}$ s $^{-1}$

- **High luminosity mode**

- $\delta p/p \sim 4 \cdot 10^{-4}$
- Momentum range = 1.5 ÷ 15 GeV/c
- Stochastic cooling  $\geq 8.9$  GeV/c
- Antiprotons number =  $10^{11}$
- Peak luminosity =  $2 \cdot 10^{32}$  cm $^{-2}$ s $^{-1}$





# PANDA experiment

D. Calvo



# The PANDA Collaboration

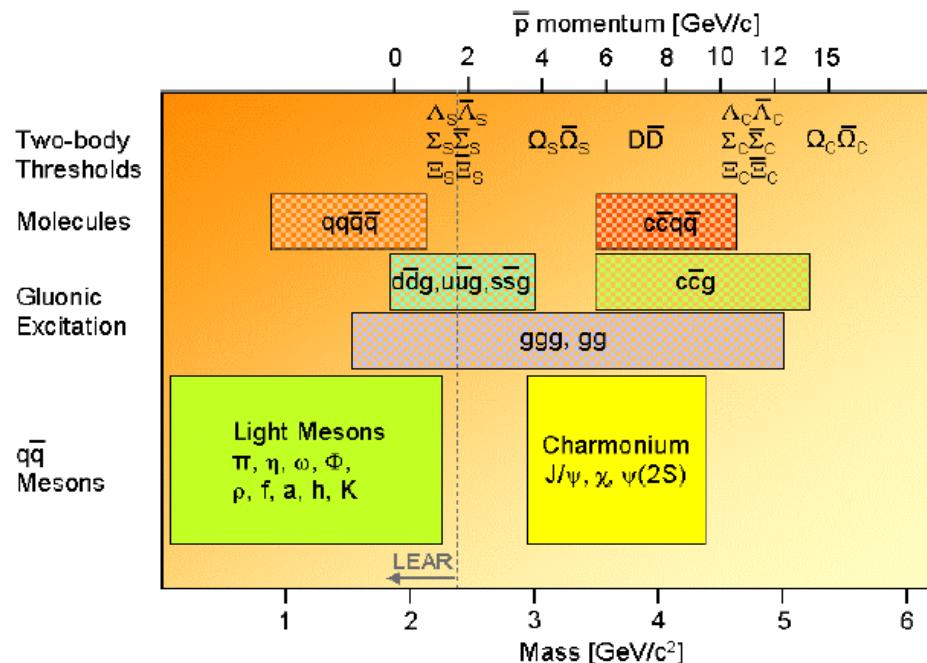
About 400 physicists from 53 institutions in 16 countries



U Basel	U & INFN Ferrara	IPN Orsay
IHEP Beijing	U Frankfurt	U & INFN Pavia
U Bochum	LNF-INFN Frascati	IHEP Protvino
IIT Bombay	U & INFN Genova	PNPI Gatchina
U Bonn	U Glasgow	U of Silesia
IFIN-HH Bucharest	U Gießen	U Stockholm
U & INFN Brescia	KVI Groningen	KTH Stockholm
U & INFN Catania	IKP Jülich I + II	U & INFN Torino
JU Cracow	U Katowice	Politecnico di Torino
TU Cracow	IMP Lanzhou	U Piemonte Orientale, Torino
IFJ PAN Cracow	U Lund	U & INFN Trieste
GSI Darmstadt	U Mainz	U Tübingen
TU Dresden	U Minsk	TSL Uppsala
JINR Dubna (LIT,LPP,VBLHE)	ITEP Moscow	U Uppsala
U Edinburgh	MPEI Moscow	U Valencia
U Erlangen	TU München	SMI Vienna
NWU Evanston	U Münster	SINS Warsaw
	BINP Novosibirsk	TU Warsaw

# Antiproton physics program in PANDA

- Charmonium (cc) spectroscopy: precision measurements of mass, width, decay branches of all charmonium states, especially for extracting information on qq models of mesons.
- Search for gluonic excitations (charmed hybrids, glueballs) in the charmonium mass range (3 – 5 GeV/c<sup>2</sup>).
- Search for modifications of meson properties in the nuclear medium
- Precision  $\gamma$ -ray spectroscopy of single and double hypernuclei for extracting information on their structure and on the hyperon-nucleon and hyperon-hyperon interaction.
- Inverted DVCS to extract parton distributions proton form-factors at large Q<sup>2</sup> up to 25 GeV<sup>2</sup>/c<sup>4</sup> D-meson decay spectroscopy BR and decay dalitz plots CP-Violation in the D/Λ sector



# Strange and charmed candidates for identification by means of their delayed decays

particle	lifetime	decay length $c\tau$	decay channel (fraction)
$K_S^0$	895.3(6) ps	2.6842 cm	$\pi^+\pi^- ((68.95 \pm 0.14)\%)$
$D^\pm$	1.040(7) ps	311.8 $\mu\text{m}$	$e^+\text{anything} + \text{c.c.} ((17.2 \pm 1.9)\%)$ $K^-\text{anything} + \text{c.c.} ((27.5 \pm 2.4)\%)$ $K^+\text{anything} + \text{c.c.} ((5.5 \pm 1.6)\%)$ $\bar{K}^0\text{anything} + K^0\text{anything} ((61 \pm 8)\%)$ e.g. $K^-\pi^+\pi^+ + \text{c.c.} ((9.2 \pm 0.6)\%)$ $\bar{K}^0\pi^+\pi^+\pi^- + \text{c.c.} ((7.1 \pm 1.0)\%)$
$D^0$	410.3(15) fs	123.0 $\mu\text{m}$	$e^+\text{anything} + \text{c.c.} ((6.87 \pm 0.28)\%)$ $\mu^+\text{anything} + \text{c.c.} ((6.5 \pm 0.8)\%)$ $K^-\text{anything} + \text{c.c.} ((53 \pm 4)\%)$ $K^+\text{anything} + \text{c.c.} ((3.4 \pm 0.4)\%)$ $\bar{K}^0\text{anything} + K^0\text{anything} ((53 \pm 4)\%)$ e.g. $\bar{K}^0K^+K^- ((1.03 \pm 0.10)\%)$ $K^-\pi^+\pi^+\pi^- + \text{c.c.} ((7.46 \pm 0.31)\%)$ $\bar{K}^0\pi^+\pi^-\pi^0 + \text{c.c.} ((10.9 \pm 1.3)\%)$
$D_s^\pm$	490(9) fs	147.0 $\mu\text{m}$	$e^+\text{anything/c.c.} (\approx 8\%)$ $K^-\text{anything} + \text{c.c.} (\approx 13\%)$ $K^+\text{anything} + \text{c.c.} (\approx 20\%)$ $\bar{K}^0\text{anything} + K^0\text{anything} (\approx 39\%)$ e.g. $K^+K^-\pi^+ + \text{c.c.} (4.4 \pm 1.2)\%$

# Strange and charmed candidates for identification by means of their delayed decays

$\Lambda$	26.32(20) ps	7.69 cm	$p\pi^- ((63.9 \pm 0.5)\%)$
$\Sigma^+$	80.18(26) ps	2.404 cm	$p\pi^0 ((51.57 \pm 0.30)\%)$ $n\pi^+ ((48.31 \pm 0.30)\%)$
$\Sigma^-$	147.9(11) ps	4.434 cm	$n\pi^- ((99.848 \pm 0.005)\%)$
$\Xi^-$	163.9(15) ps	4.91 cm	$\Lambda\pi^- ((99.887 \pm 0.035)\%)$
$\Omega^-$	82.1(11) ps	2.461 cm	$\Lambda K^- ((67.8 \pm 0.7)\%)$ $\Xi^0\pi^- ((23.6 \pm 0.7)\%)$ $\Xi^-\pi^0 ((8.6 \pm 0.4)\%)$
$\Lambda_c^+$	200(6) fs	59.9 $\mu$ m	$p\bar{K}^0 ((2.3 \pm 0.6)\%)$ $pK^-\pi^+ ((5.0 \pm 1.3)\%)$ $\Lambda\pi^+\pi^+\pi^- ((3.3 \pm 1.0)\%)$ $\Sigma^0 + \pi^+\pi^- ((3.6 \pm 1.0)\%)$
$\Xi_c^0$	112(13) fs	33.6 $\mu$ m	$\Xi^-\pi^+ (not known)$

# Production rates ( $1-2(\text{fb})^{-1}/\text{y}$ )

<u>Final State</u>	<u>cross section</u>	<u># rec. events/y</u>
$\eta_c \rightarrow K_S^0 K^\pm \pi^\mp$	$10 \text{ nb}$	$10^7$
$\Lambda \bar{\Lambda}$	$50 \mu\text{b}$	$10^{10}$
$\Xi \bar{\Xi} (\rightarrow_{\Lambda\Lambda} A)$	$2 \mu\text{b}$	$10^8 (10^5)$
$\psi(3770) \rightarrow D \bar{D}$	$3 \text{ nb}$	$10^7$
$J/\psi (\rightarrow e^+e^-, \mu^+\mu^-)$	$630 \text{ nb}$	$10^9$
$\chi_2 (\rightarrow J/\psi + \gamma)$	$3.7 \text{ nb}$	$10^7$
$\Lambda_c \bar{\Lambda}_c$	$20 \text{ nb}$	$10^7$
$\Omega_c \bar{\Omega}_c$	$0.1 \text{ nb}$	$10^5$
$\sigma_T(p \bar{p})$	$70 \text{ mb}$	

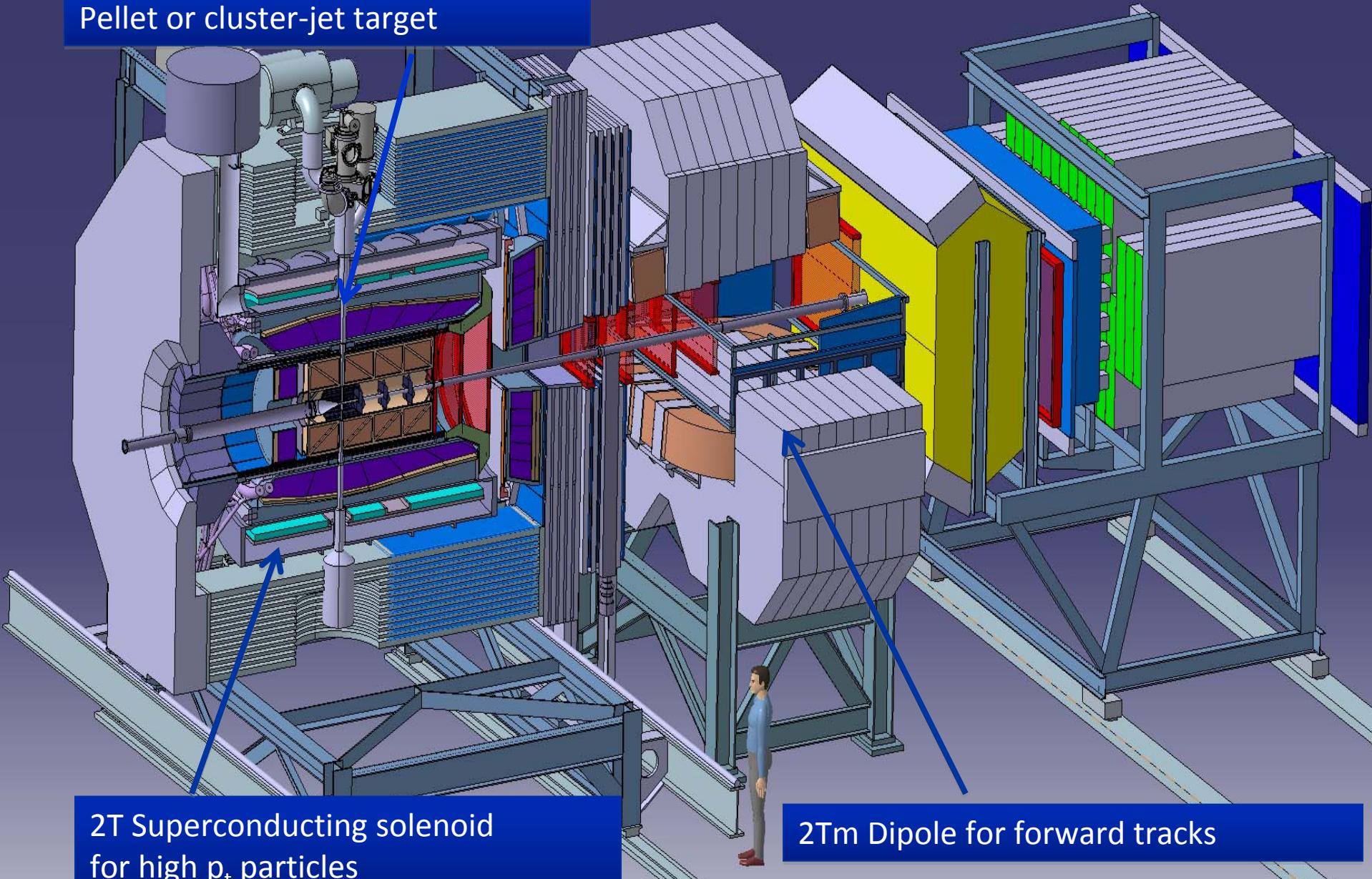
Key elements : Low multiplicity events

Possibility to trigger on defined final states

# Multi-purpose Detector requirements

- Nearly  $4\pi$  solid angle
- High rate capabilities ( $2 \cdot 10^7$  annihilations /s)
- Efficient event selection
  - Continuous readout
- Moment resolution (1%)
- Vertex info for D,  $K_s^0$ , L ( $c_\tau = 317 \mu\text{m}$  for  $D^{+ -}$ )
  - good tracking
- Good PID ( $\gamma$ , e, m,  $\pi$ , k, p)
  - Cherenkov, tof,  $dE/dx$
- $\gamma$ -detection 1 MeV  $\div$  10 GeV
  - Crystal Calorimeter
- Modular design ( hypernuclear experiments )

Pellet or cluster-jet target

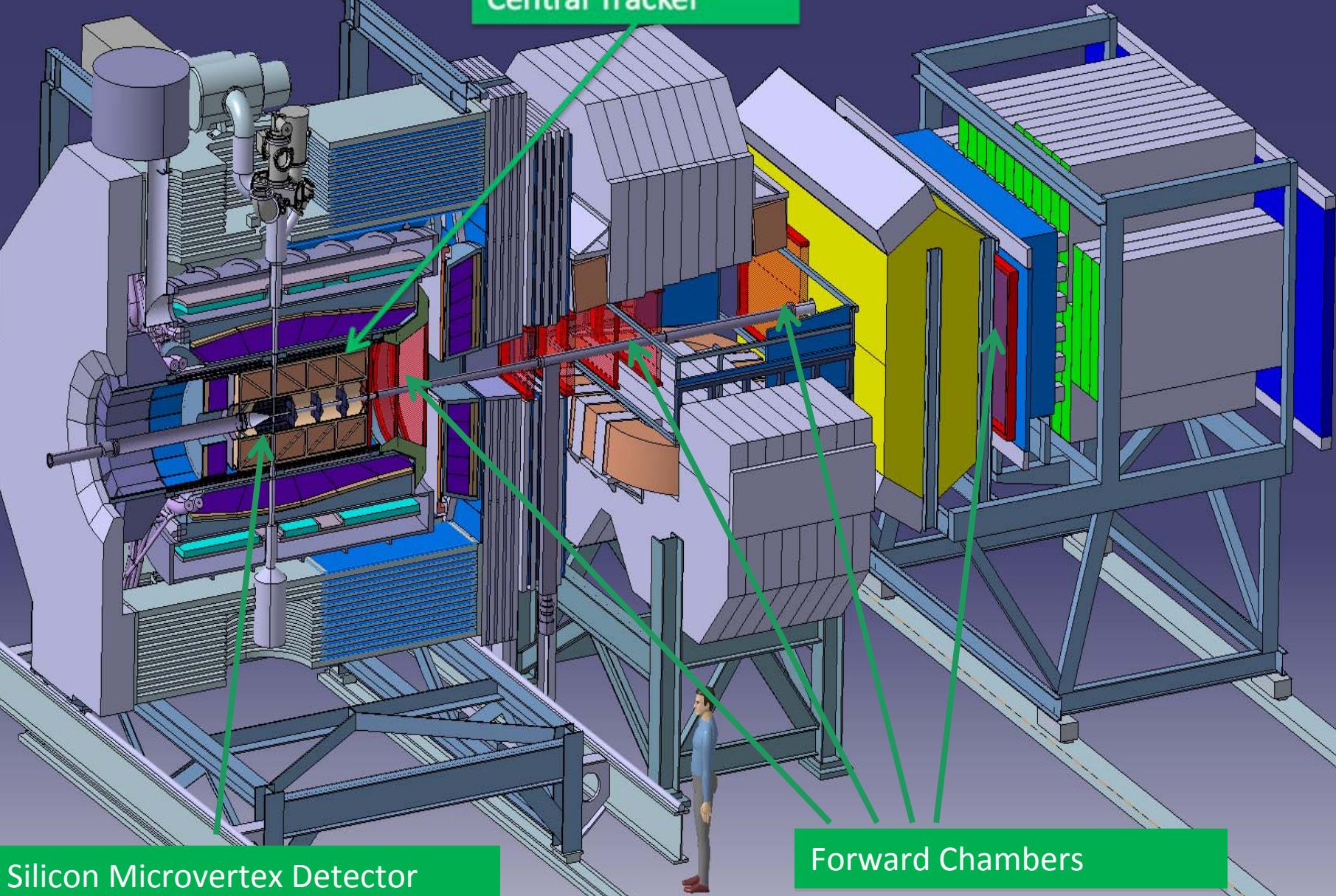


2T Superconducting solenoid  
for high  $p_t$  particles

2Tm Dipole for forward tracks

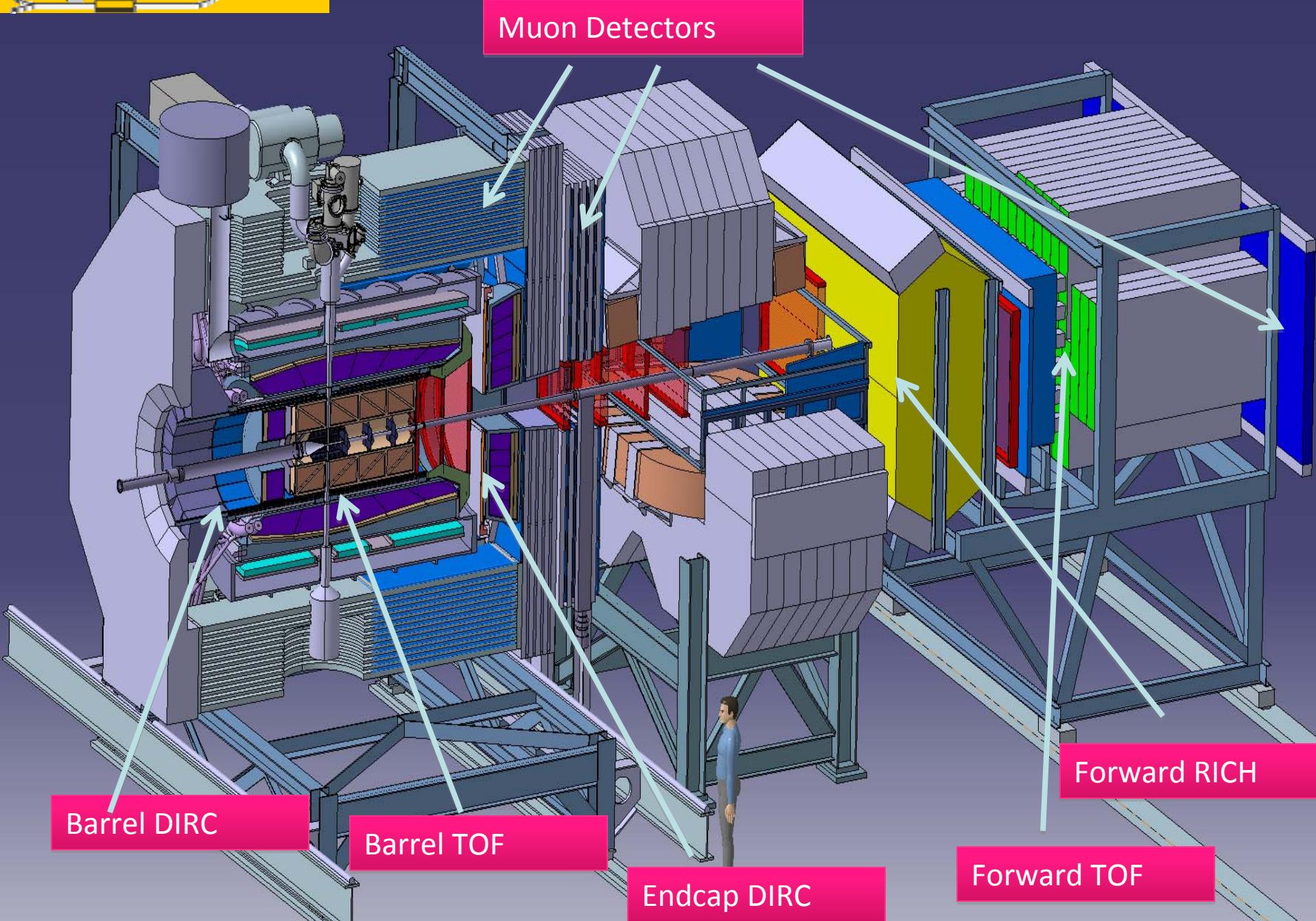


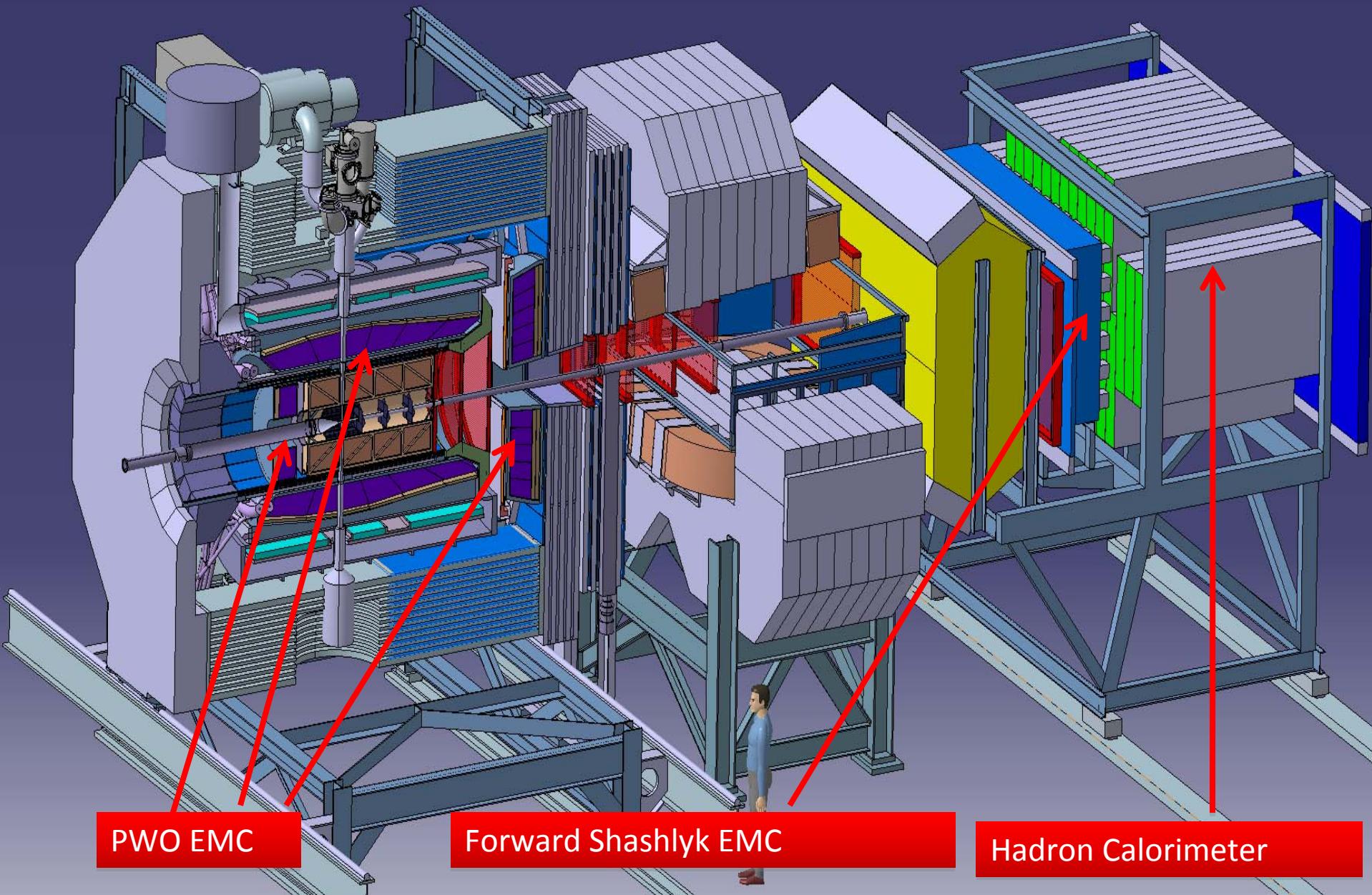
Central Tracker



Silicon Microvertex Detector

Forward Chambers



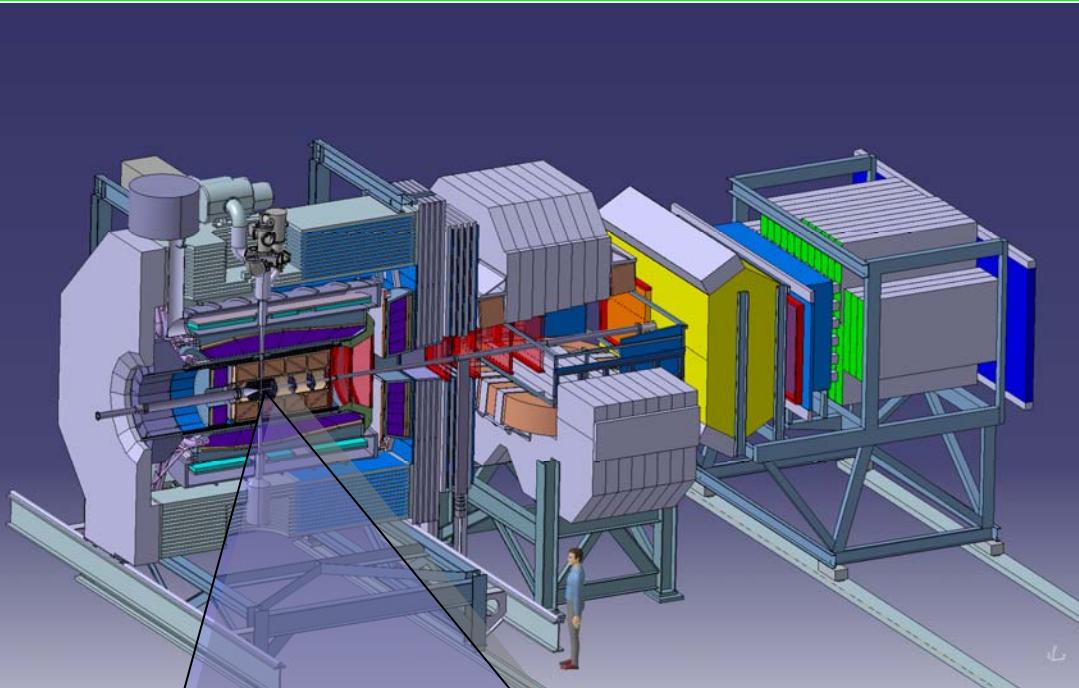


PWO EMC

Forward Shashlyk EMC

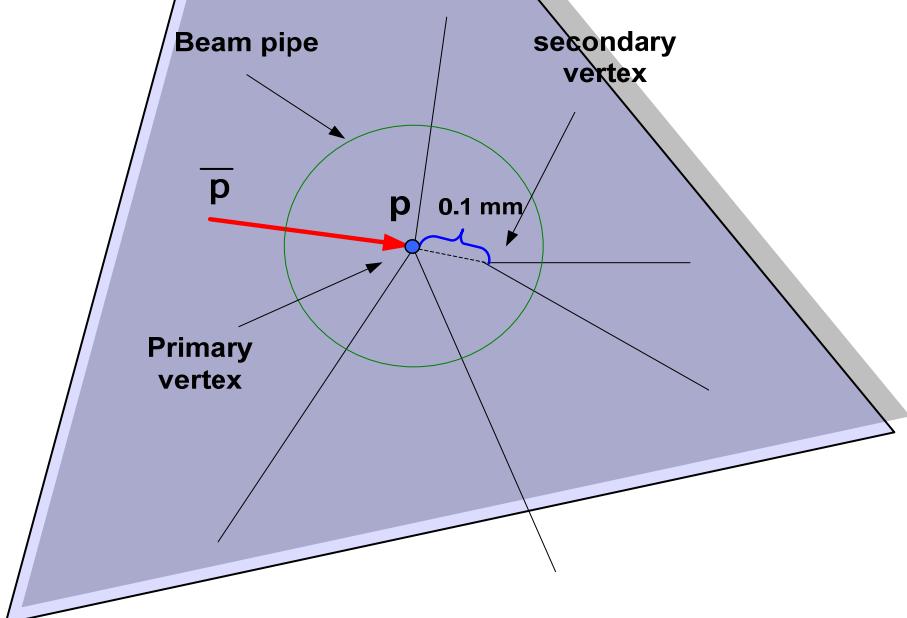
Hadron Calorimeter

# MVD requirements



Benchmark experiments that require optimum performance of the vertex tracking

reaction channel	detected particle
$\bar{p}p \rightarrow \phi\phi$	$2K^+ 2K^-$
$\bar{p}p \rightarrow \eta_c$	$K^\pm \pi^\mp K_S^0$
$\bar{p}p \rightarrow \psi(3770)$	$D\bar{D}$ $\rightarrow K's \text{ and } \pi's$
$\bar{p}A \rightarrow D\bar{D} X$	$D$

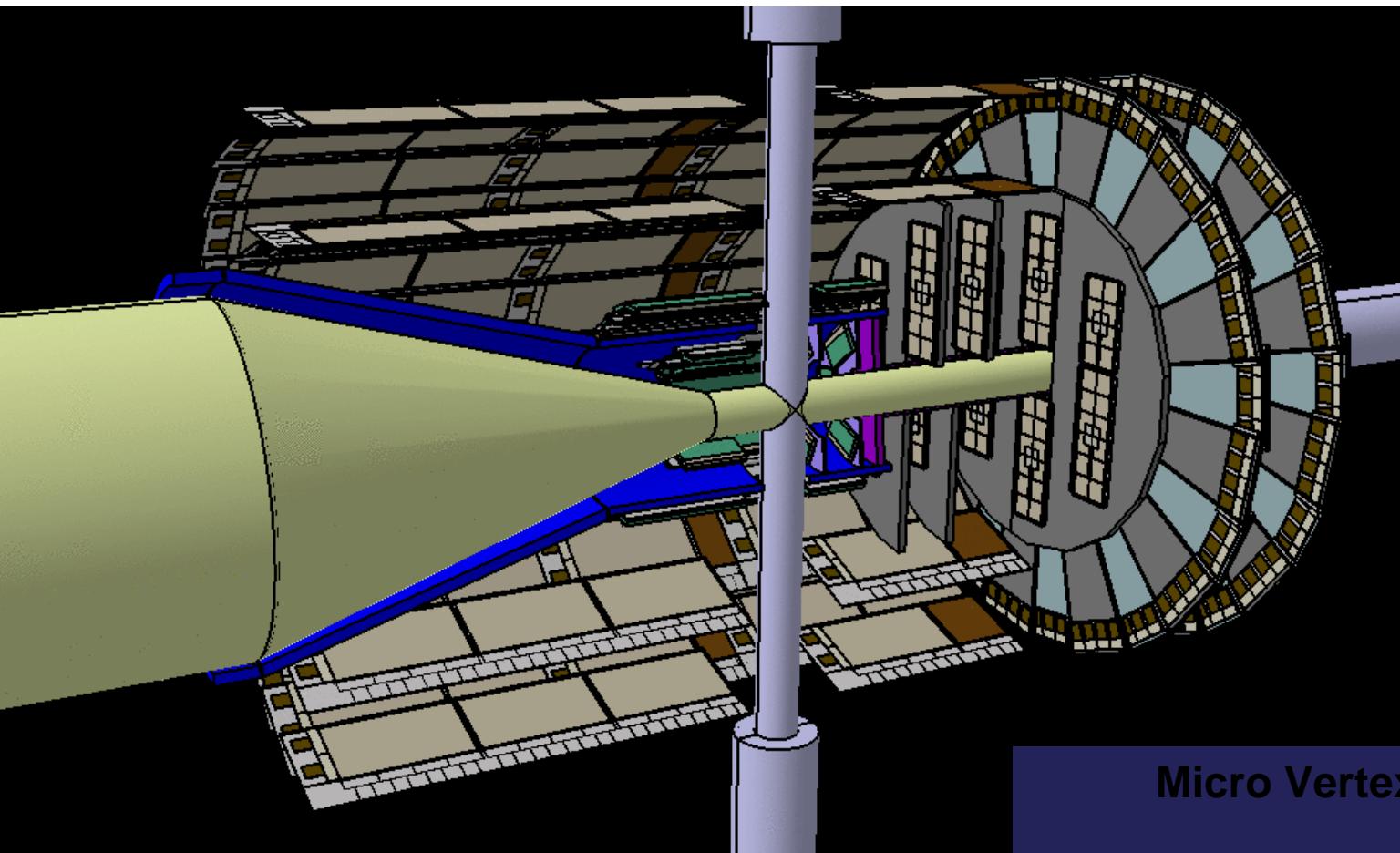


The most serious challenge will be D identification due to the very short decay lengths of these mesons

# MVD requirements

- Good spatial resolution in r-phi
  - Momentum measurement of pions from D\* decays
- Good spatial resolution specially in z
  - Vertexing, D-tagging
- Good time resolution
  - 20 ns (at 50 MHz clock) with  $2 \cdot 10^7$  ann/s
- Triggerless readout
  - No first level hardware trigger, clock at 50 MHz
- Amplitude measurement
  - Improvement of resolution with  $dE/dx$  to improve particle ID
- Low material budget
  - low momentum particles (starting from some hundreds of MeV/c) ( $< 1\% X_0$  for each layer)
- Radiation hardness ( $\sim 4 \cdot 10^{14} n_{1\text{MeV eq}}/\text{cm}^2$ )
  - Depends on target material

# MVD layout



**Micro Vertex Detector**

4 barrels

*Inner layers:* hybrid pixels

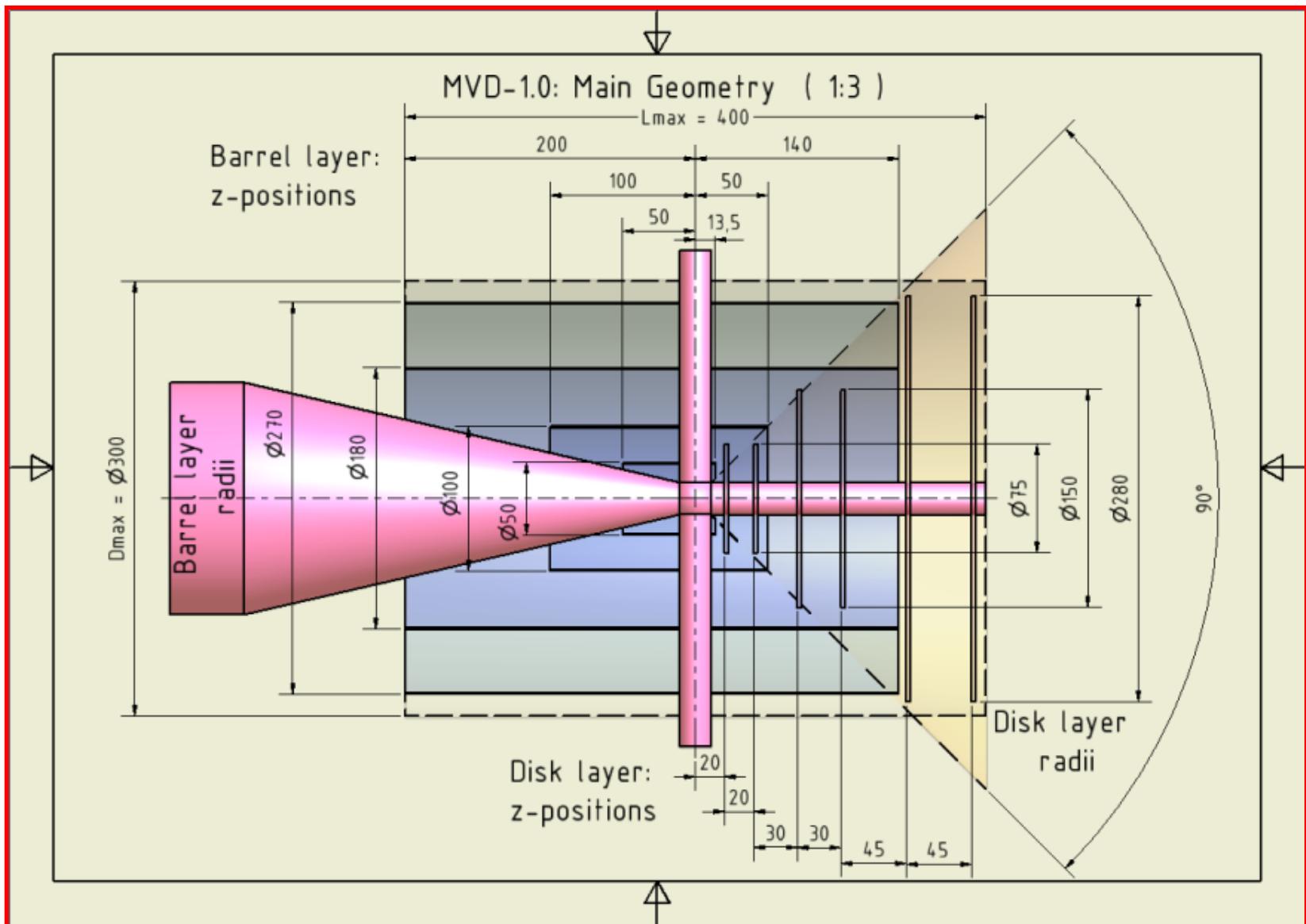
*Outer layers:* double sided strips

and 6 forward disks

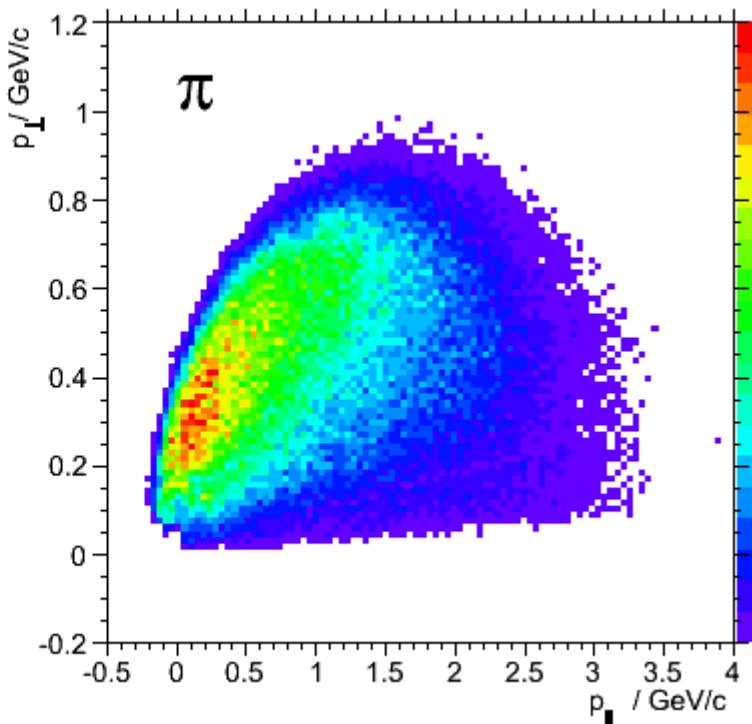
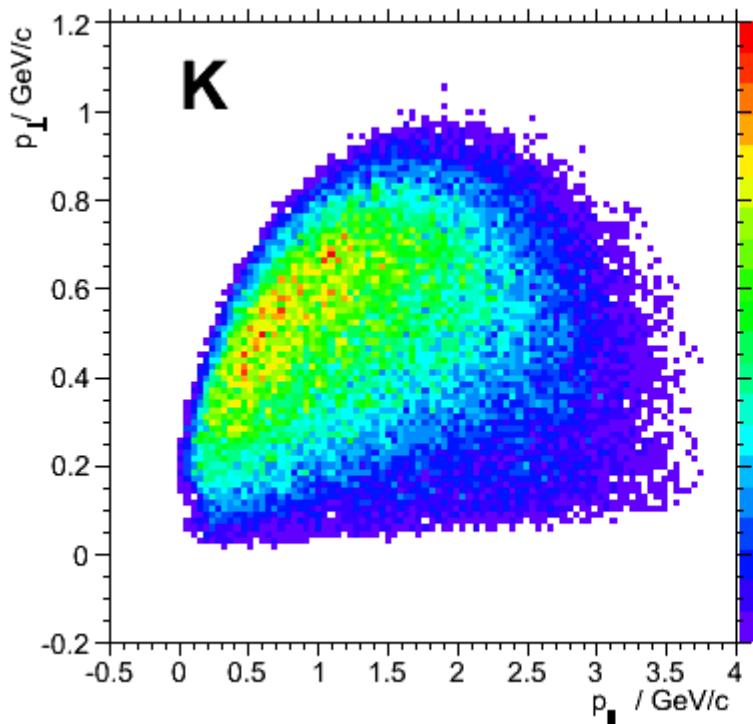
*4 disks:* hybrid pixels

*2 disks:* pixel and strips mixed

# MVD geometry

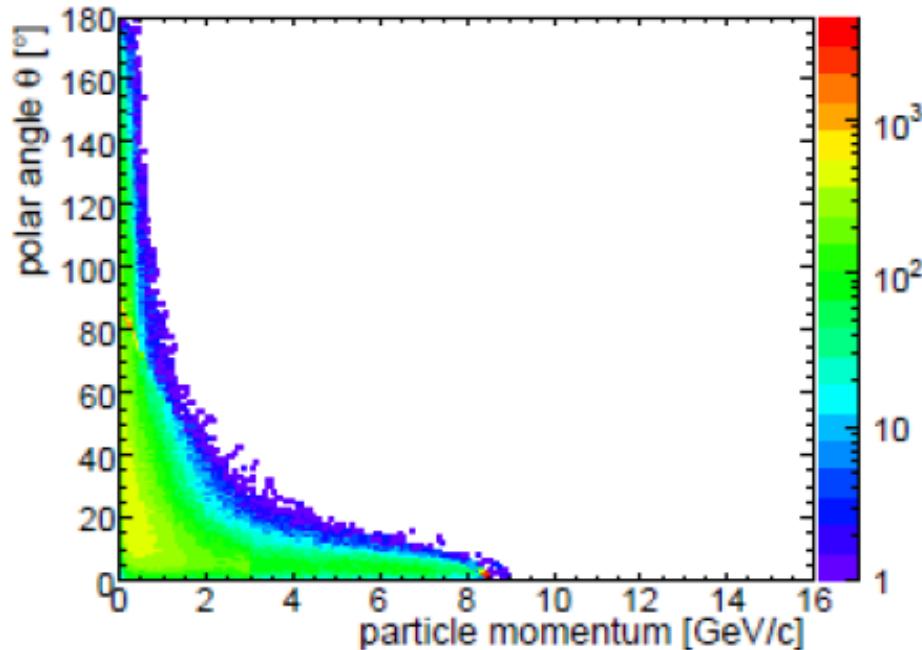


# Kaon and pion momentum distribution from D decay



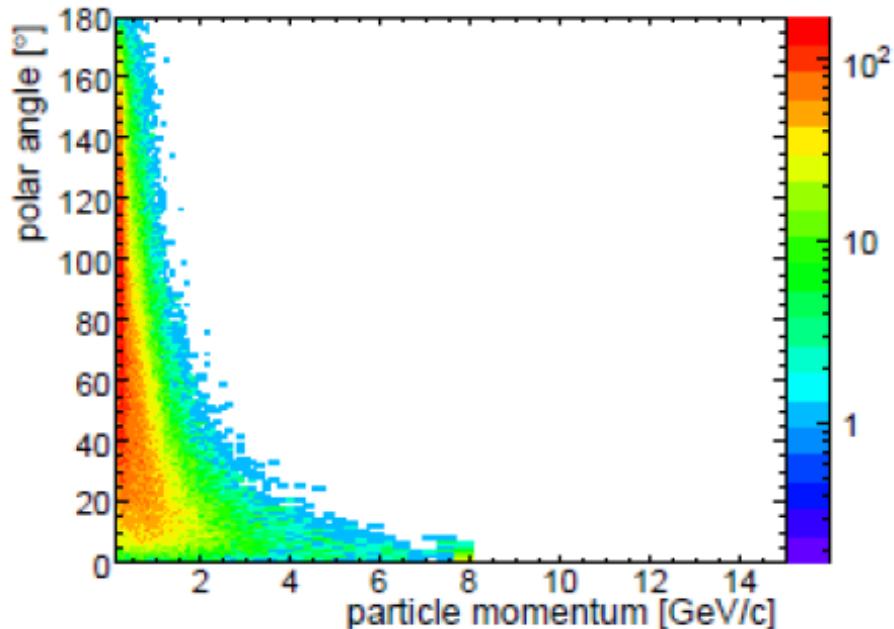
Transverse vs. longitudinal momentum of  $k$  and  $\pi$  from the reaction  $\text{antipp} \rightarrow \text{DantiD}$  at the beam momentum of 6.7 GeV/c. The detected charged particles are produced in the decay of the D mesons via  $D^{+-} \rightarrow K^{-+} \pi^+ \pi^-$

# Momentum distribution

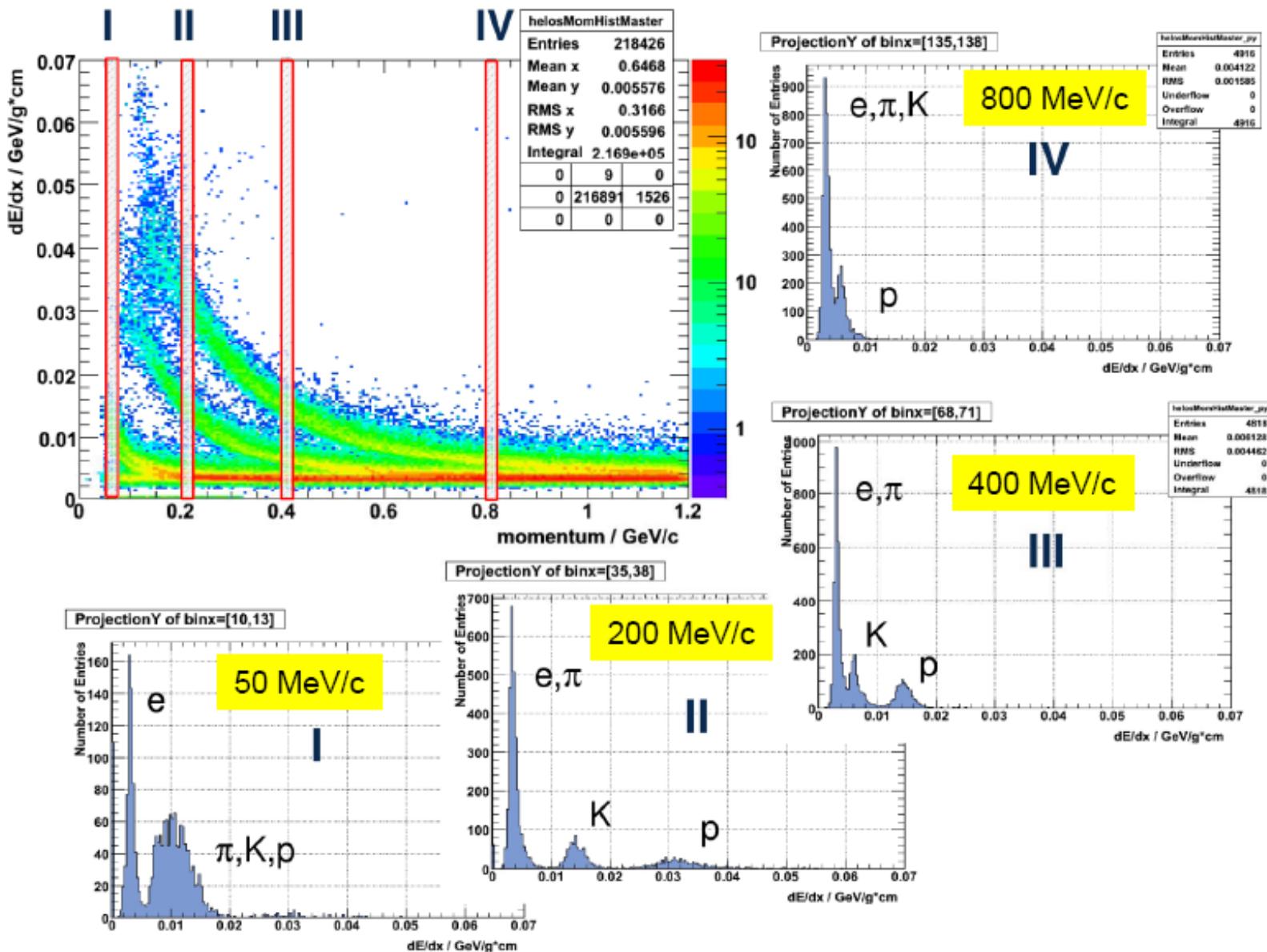


antipp @8 GeV/c

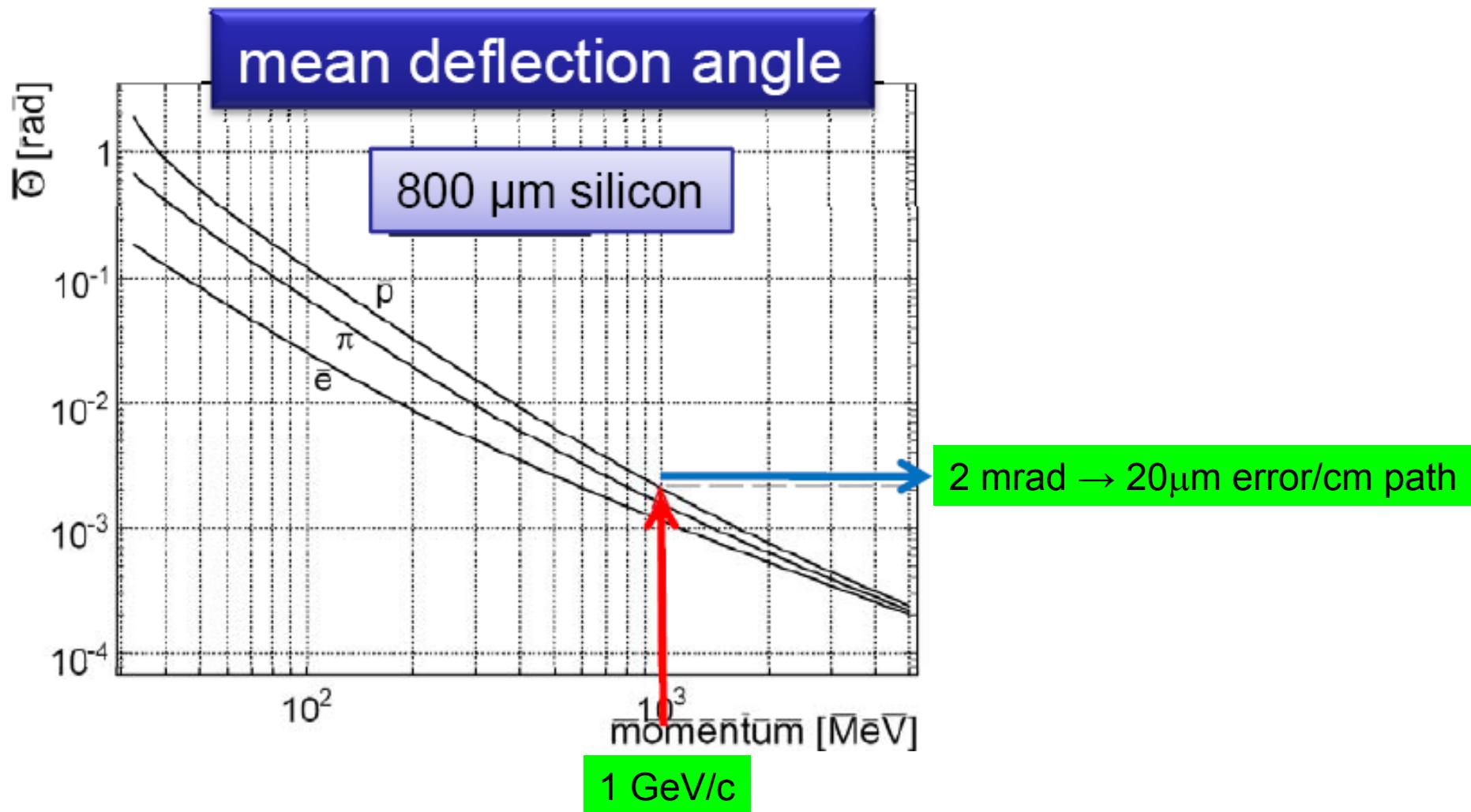
antipAu @8 GeV/c



# PID with MVD

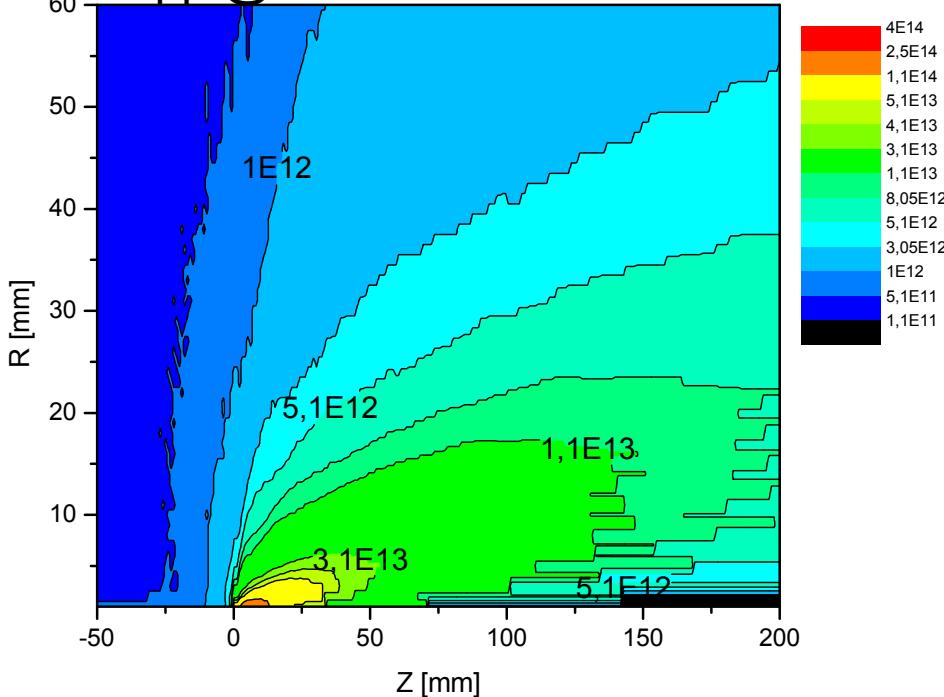


# Multiple scattering

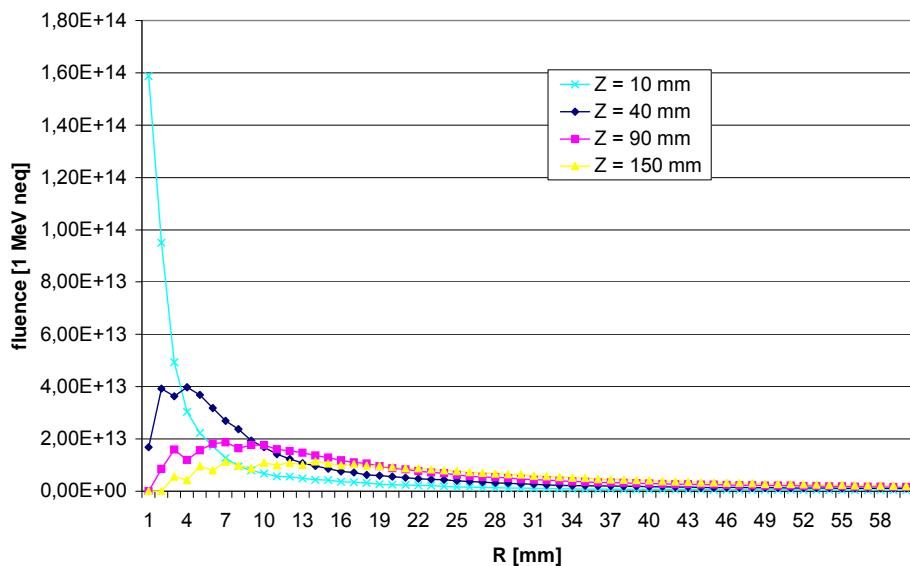
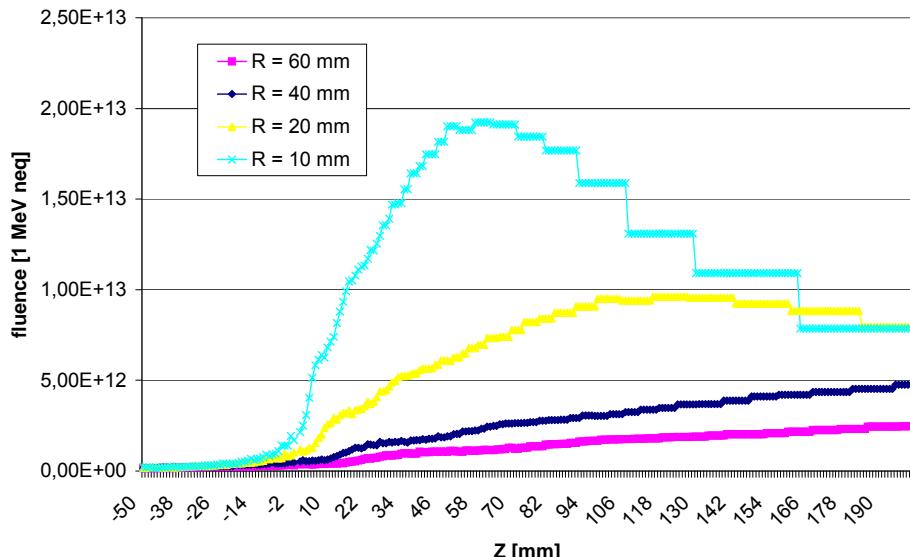


# Radiation load I

Antipp @ 5 GeV/c

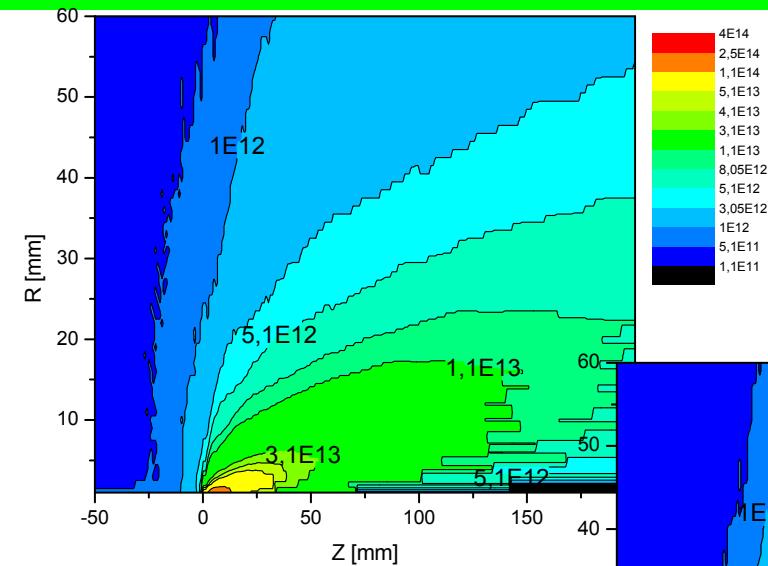


- particles are peaked in forward direction
- radial distribution  $\sim 1/R^2$
- nearly no damage in backward parts of the MVD
- annual fluence well below  $10^{13} n/cm^2$  for all relevant parts

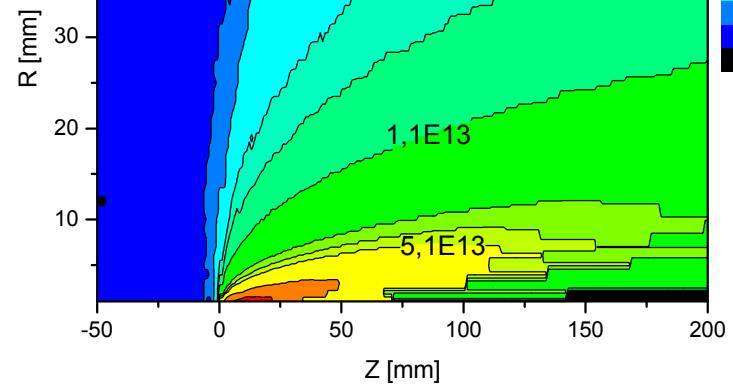
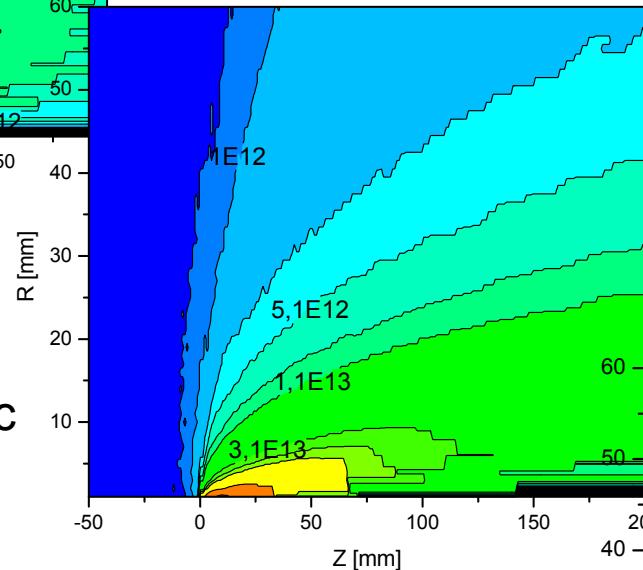


# Radiation load II

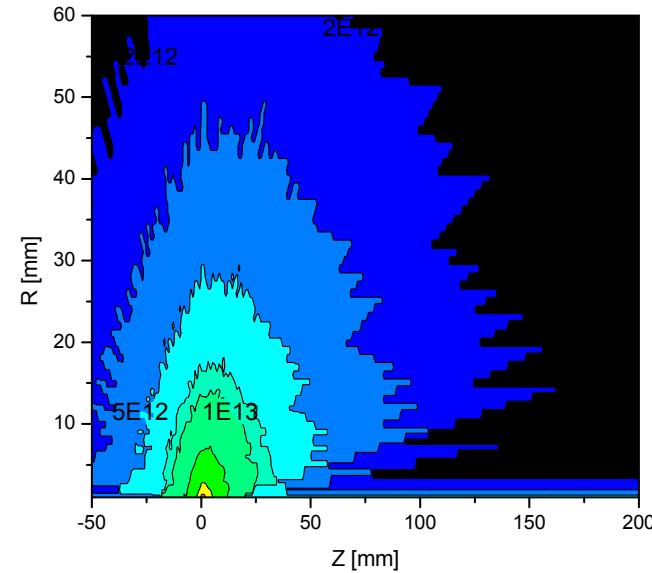
Antipp @ 5 GeV/c



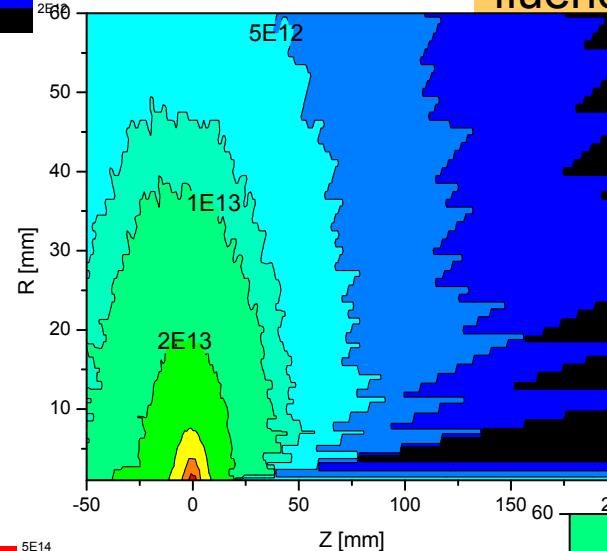
Antipp @ 10 GeV/c



# Radiation load III

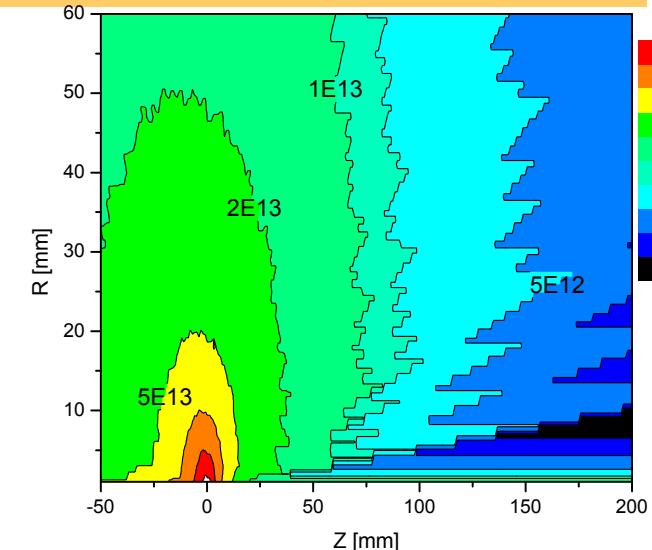


antipC @ 4.05 GeV/c  
fluence below  $1 \times 10^{13} \text{ n/cm}^2$

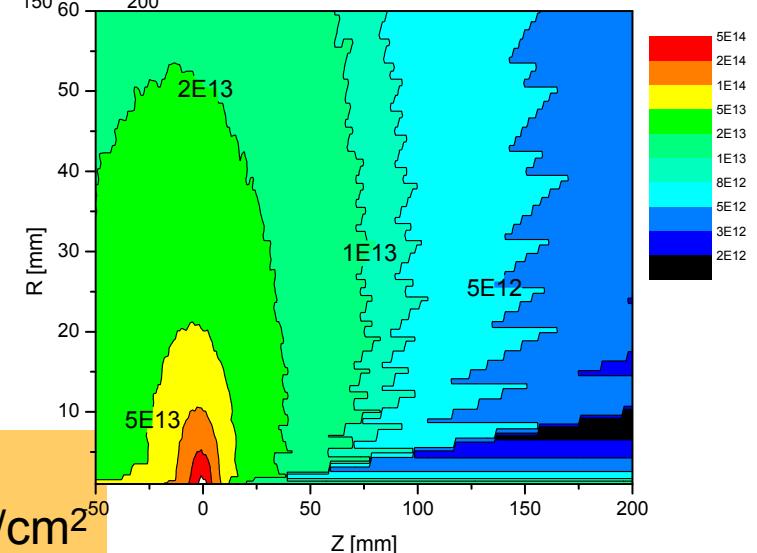


antipCu @ 4.05 GeV/c  
fluence below  $2.5 \times 10^{13} \text{ n/cm}^2$

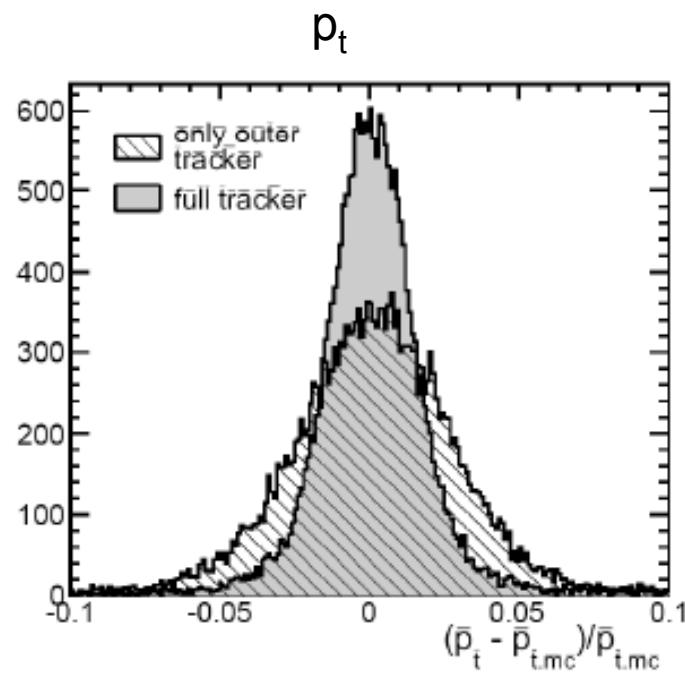
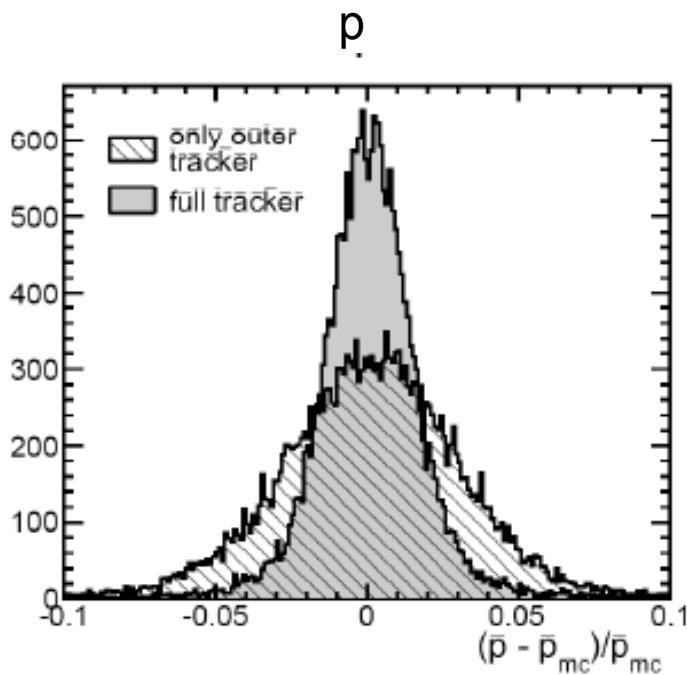
antipAu @ 4.05 GeV/c  
fluence below  $6 \times 10^{13} \text{ n/cm}^2$



antipPb @ 4.05 GeV/c  
fluence below  $6 \times 10^{13} \text{ n/cm}^2$



# Momentum resolution of PANDA detector

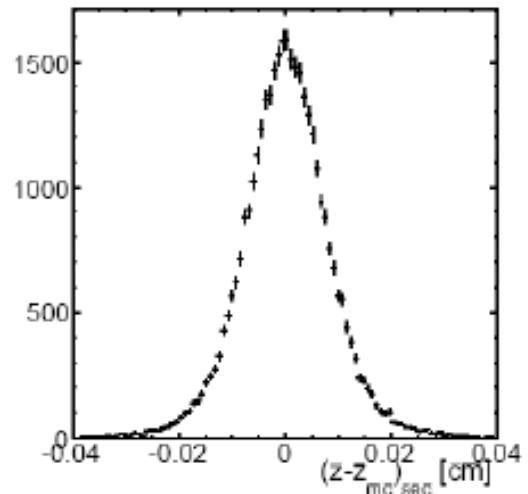
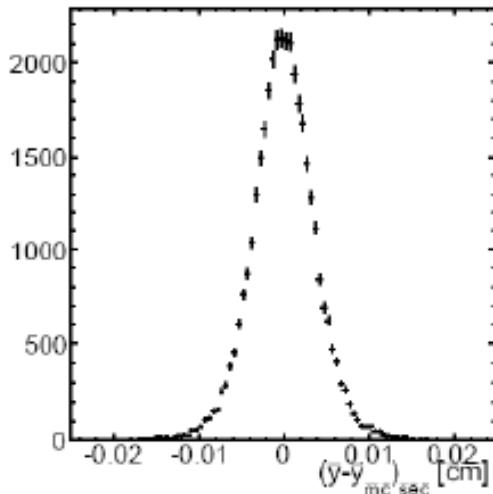
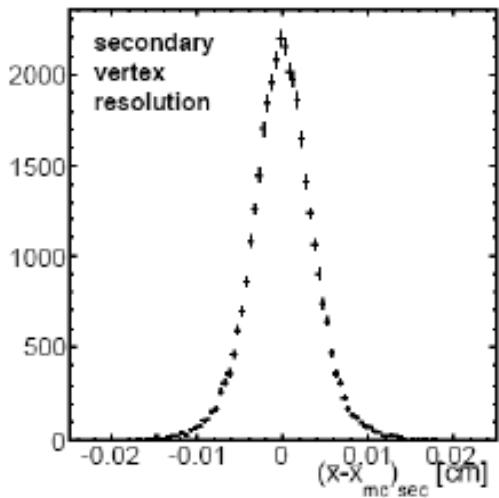


R. Jäkel PhD thesis in preparation

$\sigma(p)$ [1GeV/c pions] without MVD	= 2.6%
$\sigma(p)$ [1GeV/c pions] with MVD	= 1.4%

# Secondary vertex resolution

antip p  $\rightarrow D^+D^-$



R. Jäkel PhD thesis in preparation

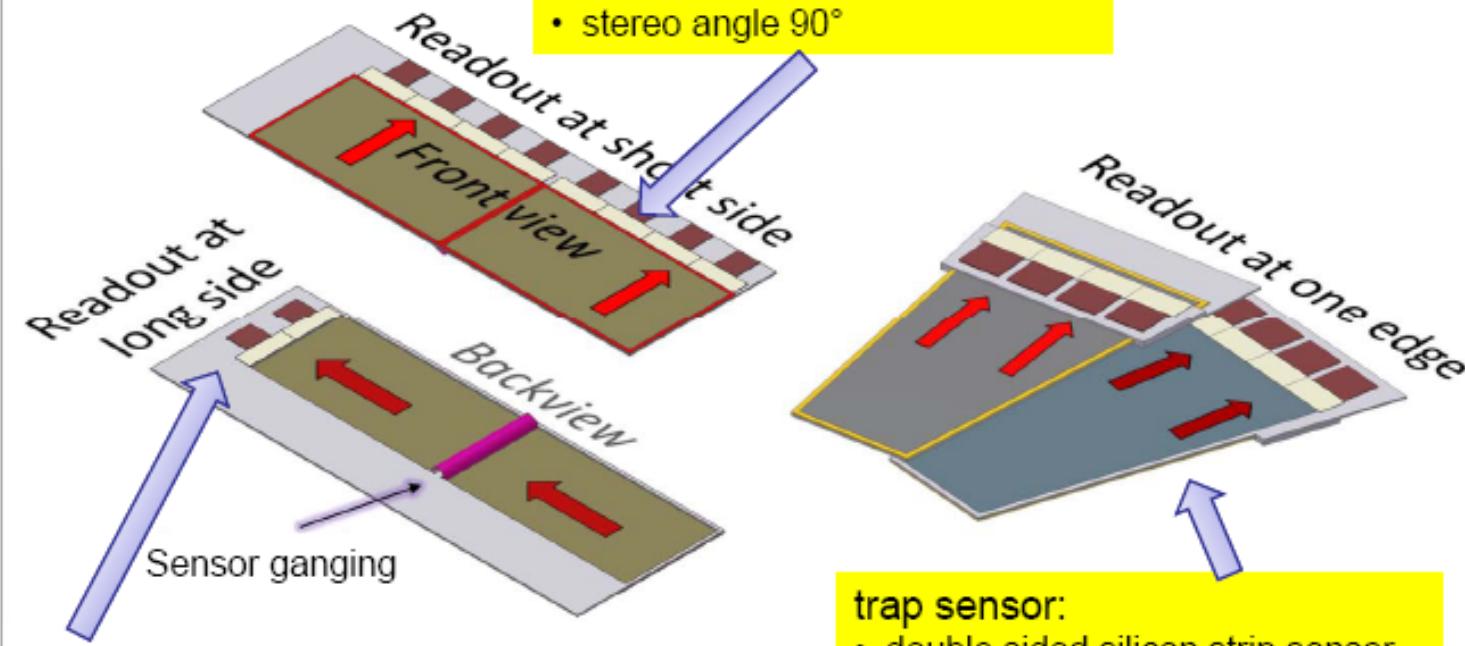
- Fully reconstructed  $D^+D^-$  pairs
- Vertex resolution:
  - 35  $\mu\text{m}$  in x and y
  - 77  $\mu\text{m}$  in z (at 6.57 GeV/c beam momentum)

R. Jäkel PhD thesis in preparation

# Strips detector

## rectangular sensor:

- double sided silicon strip sensor
- pitch:  $130\ \mu\text{m}$  ( $0.65\ \mu\text{m}$ )
- size box:  $6.7 \times 3.3 \times 0.03\ \text{cm}^3$
- stereo angle  $90^\circ$



## front-end electronic:

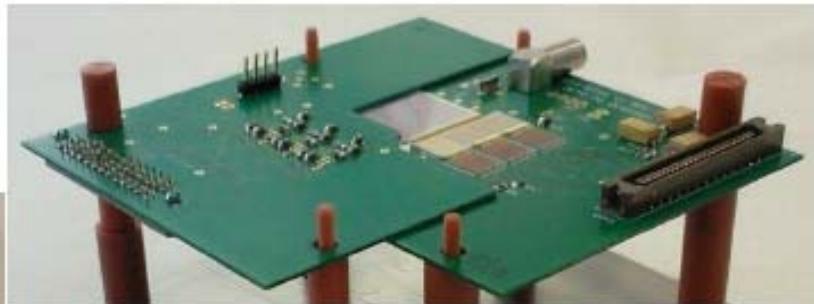
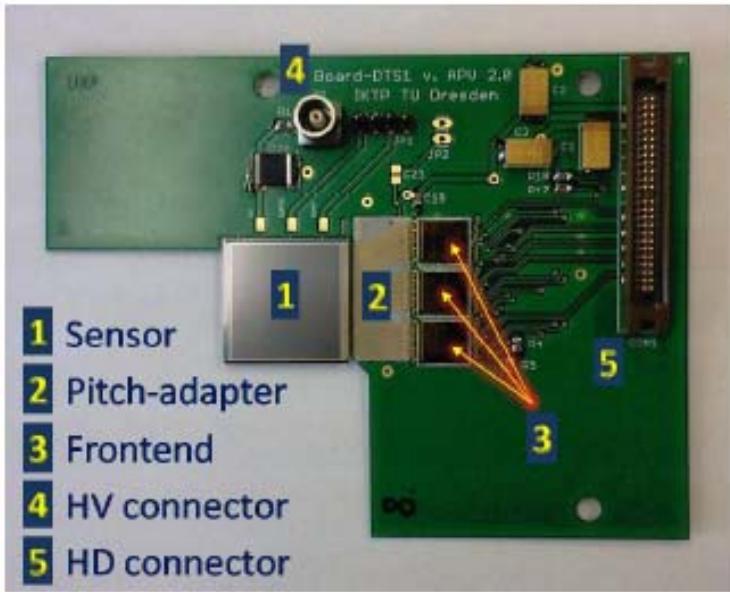
- custom development together with GSI
- untriggered readout

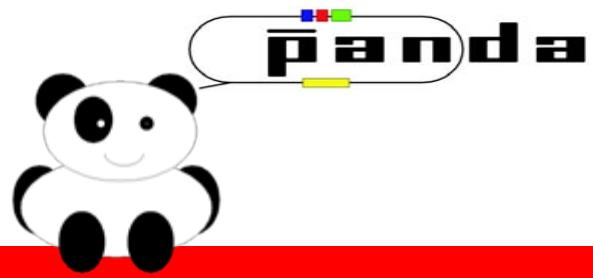
## trap sensor:

- double sided silicon strip sensor
- pitch:  $70\ \mu\text{m}$
- size box:  $6.1 \times 3.5 \times 0.03\ \text{cm}^3$
- stereo angle  $15^\circ$

# Strip prototype

First small sensor prototype with APV readout





# Pixel Detector

D. Calvo



# Pixel Detector

## Pixel Detector ( $\sim 0.12 \text{ m}^2$ ):

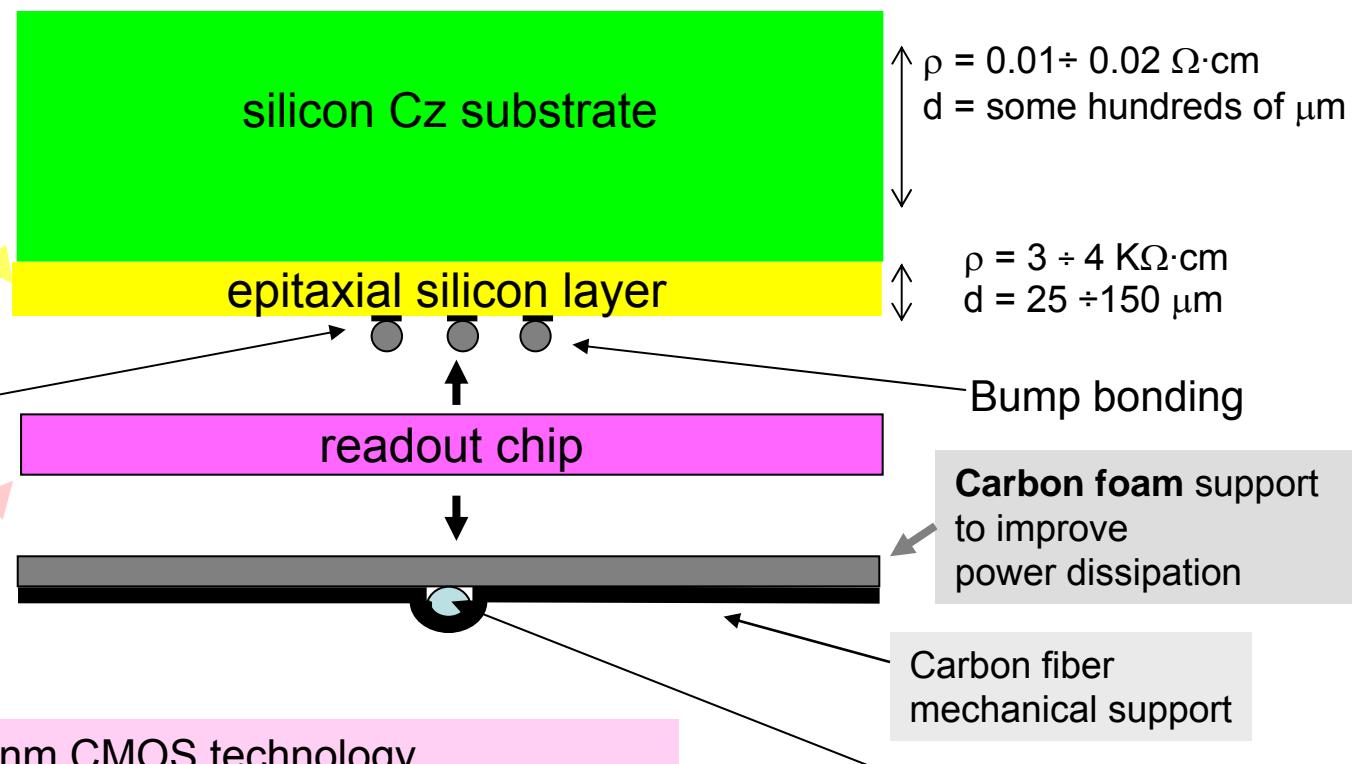
- ~ 11 Mpixel with  $100 \mu\text{m} \times 100 \mu\text{m}$  size
- ~ 1100 FE readout chip ( $\sim 100 \times 100$  pixel)
- continuous data transmission without trigger
- maximum chip rate:  $\sim 12.3 \text{ MHz}$  for pbar-Au at  $15 \text{ GeV}/c$
- maximum chip data rate:  $\sim 0.6 \text{ Gb/s}$  ( $\sim 50 \text{ bit/pixel}$ )
- energy loss measurement: Time over Threshold; dynamic range:  $\rightarrow 100 \text{ fC}$

# Standard hybrid technology

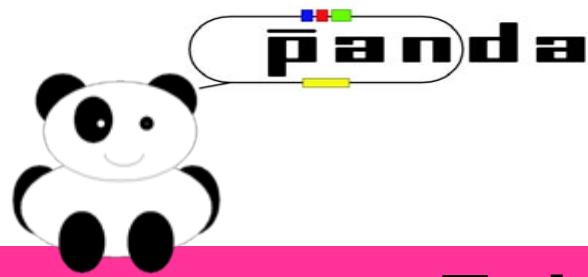
**THIN PIXEL SENSORS**  
( $< 150 \mu\text{m}$ ) realized with  
EPITAXIAL SILICON  
material (FBK)  
(At LHC experiment Si  
sensors 200  $\mu\text{m}$  thick. At  
RD50 epitaxial silicon  
material only for diodes)

The thinning starts from this  
side, reducing the substrate  
to tens of  $\mu\text{m}$ .

Several processes  
for defining geometry  
and for obtaining pixel sensors  
are made on this side



**ASIC** developed by the 130 nm CMOS technology  
with triggerless readout.  
Up to now only in 250 nm CMOS technology  
(see LHC experiment with trigger )



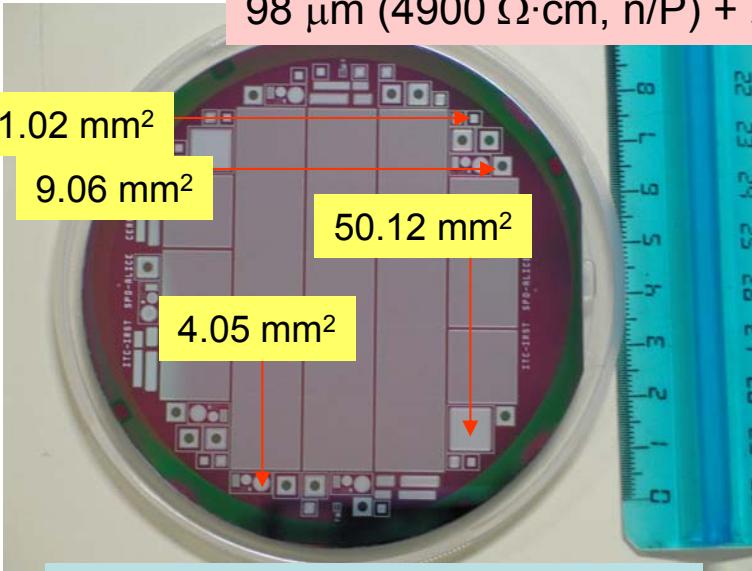
# Epitaxial silicon devices

D. Calvo



# Diodes and single chip sensor from epi-wafers

49  $\mu\text{m}$  (4060  $\Omega\cdot\text{cm}$ , n/P) + 500  $\mu\text{m}$  Cz substrate (0.01-0.02  $\Omega\cdot\text{cm}$ , n<sup>+</sup>/Sb)  $\rightarrow$  100  $\mu\text{m}$   
74  $\mu\text{m}$  (4570  $\Omega\cdot\text{cm}$ , n/P) + 500  $\mu\text{m}$  Cz substrate (0.01-0.02  $\Omega\cdot\text{cm}$ , n<sup>+</sup>/Sb)  $\rightarrow$  120  $\mu\text{m}$   
98  $\mu\text{m}$  (4900  $\Omega\cdot\text{cm}$ , n/P) + 500  $\mu\text{m}$  Cz substrate (0.01-0.02  $\Omega\cdot\text{cm}$ , n<sup>+</sup>/Sb)  $\rightarrow$  150  $\mu\text{m}$

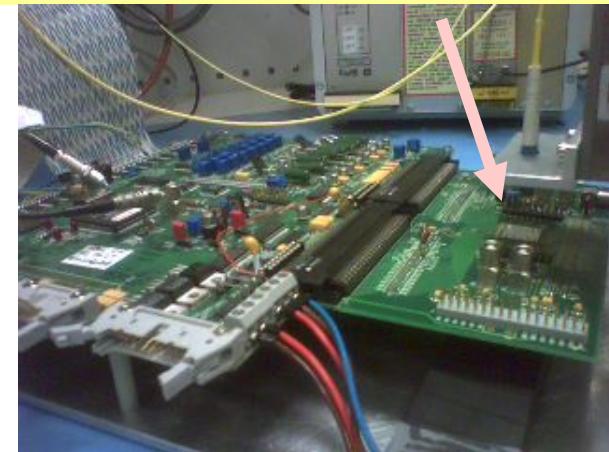


with the ALICE layout at FBK

300  $\mu\text{m}$  FZ wafer have been used as reference

## Single chip assembly

- ✓ pixel obtained with the ALICE masks (50  $\mu\text{m} \times 425 \mu\text{m}$ )
- ✓ test performed using ALICE pixel readout chip and test system in collaboration with P. Riedler

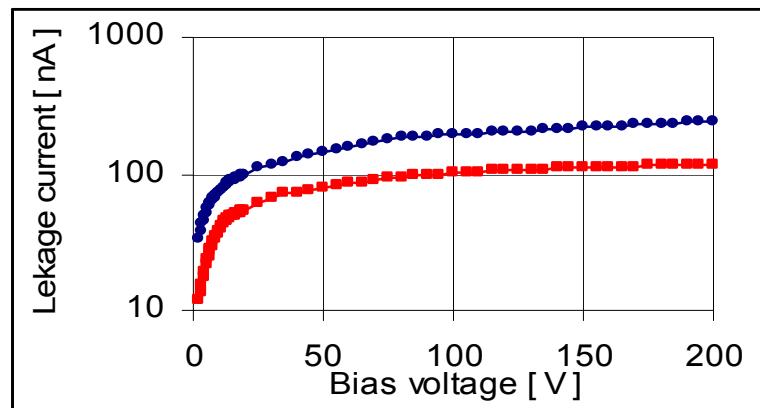


## Diodes

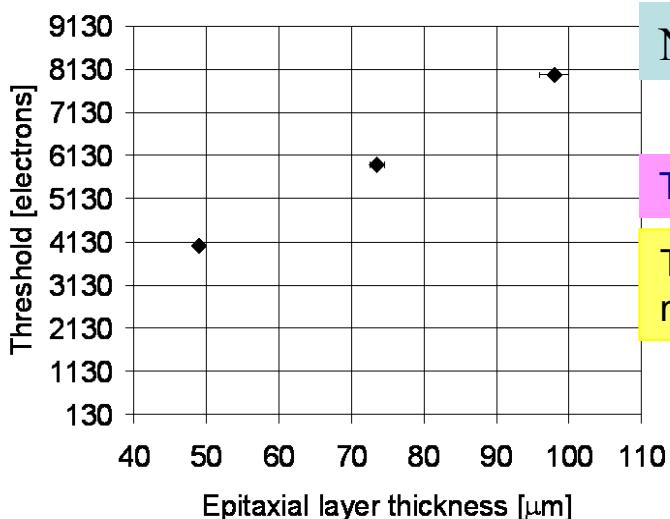
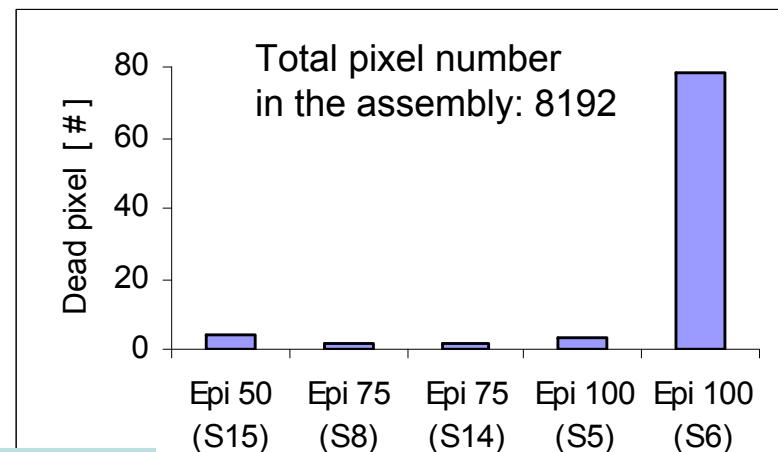
Test of radiation damage with neutrons from Pavia nuclear reactor. Equivalent fluence values on the diodes :  
 $5.13 \times 10^{13}$ ,  $1.54 \times 10^{14}$ ,  $5.13 \times 10^{14}$  n(1MeV<sub>eq</sub>)/cm<sup>2</sup>  
corresponding to 1, 3 and 10 years of PANDA lifetime

# Results from thin Si-epitaxial pixel assemblies

Epi 75 and Epi 50



Test performed with a  $^{90}\text{Sr}$  source  
to verify the bump bonding process



NIM A594 (2008) 29–32

Dead pixel %  $\leq 0.05\%$ ;  
 $\leq 1\%$  (worst case)

Test performed with a  $^{90}\text{Sr}$  source

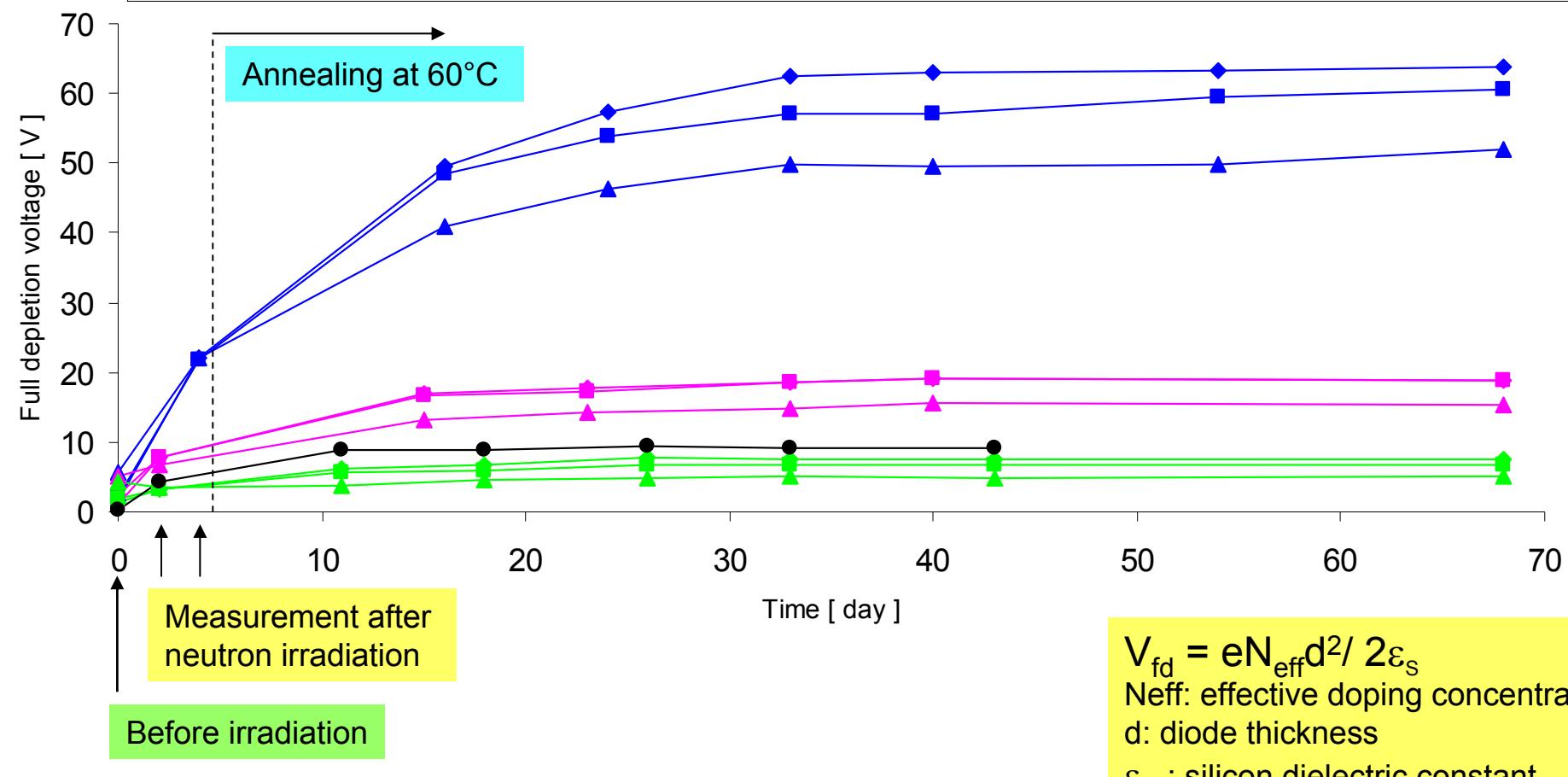
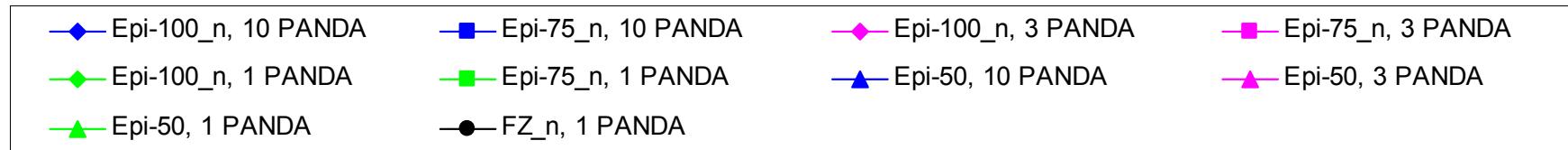
Threshold values in electrons corresponding to the Landau most probable value for the different epitaxial layer thicknesses

Confirmed by the linearity of the result, charge sharing is not a major issue – despite the  $50\mu\text{m}$  pixel width – due to the fact that the active thickness is equally limited

Taking 22.500 electrons for a true MIP in  $300\mu\text{m}$  of silicon  $\rightarrow$  7500 electrons from  $100\mu\text{m}$  of silicon,  
the beta source should raise that value somewhat ( about 8000 electrons in  $100\mu\text{m}$ )  
the agreement seems more than satisfactory.

# Results from radiation damage test: full depletion voltage normalized to epi50

Equivalent fluence values on the diodes :  $5.13 \times 10^{13}$   $1.54 \times 10^{14}$   $5.13 \times 10^{14}$  n( $1\text{MeV}_{\text{eq}}$ )/ $\text{cm}^2$   
corresponding to 1 3 and 10 years of PANDA lifetime

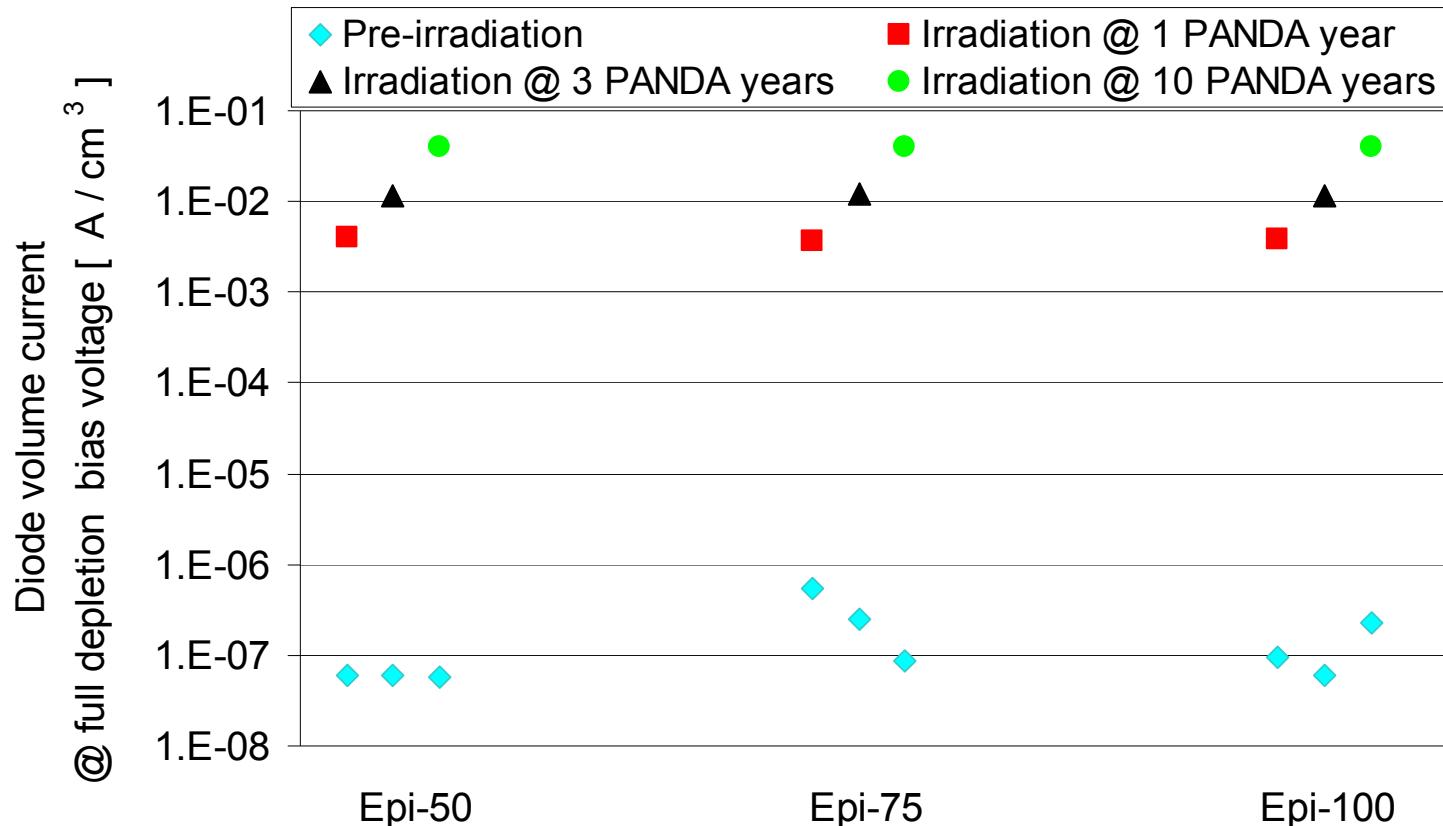


$$V_{fd} = eN_{eff}d^2/2\varepsilon_s$$

Neff: effective doping concentration  
d: diode thickness  
 $\varepsilon_s$  : silicon dielectric constant

# Results from radiation damage test: the radiation damage constant

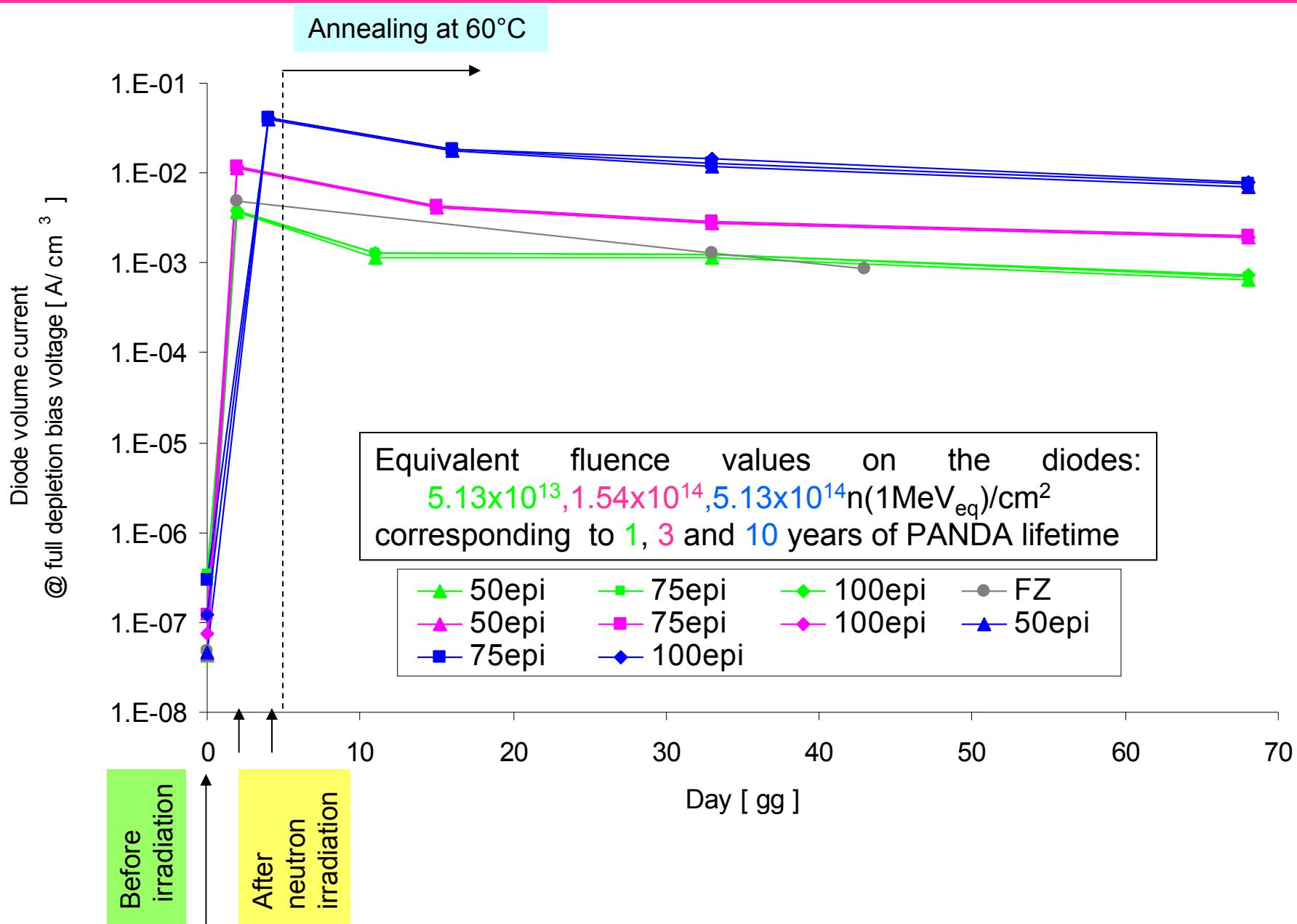
Equivalent fluence values on the diodes :  $5.13 \times 10^{13}$ ,  $1.54 \times 10^{14}$ ,  $5.13 \times 10^{14}$  n(1 MeV<sub>eq</sub>)/cm<sup>2</sup> corresponding to 1, 3 and 10 years of PANDA lifetime

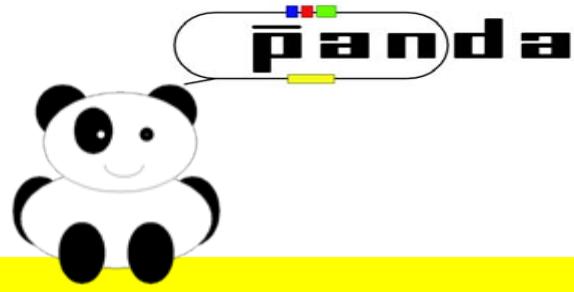


The radiation damage constant is  
 $\alpha = \Delta J/\Phi = 7.6(\pm 0.3) \times 10^{-17}$  A/cm for all diodes.

Lekage current < 50 nA/pixel (100  $\mu\text{m} \times 100\mu\text{m}$  size, 100  $\mu\text{m}$  thick)

# Results from radiation damage test: diode volume current @ full depletion voltage



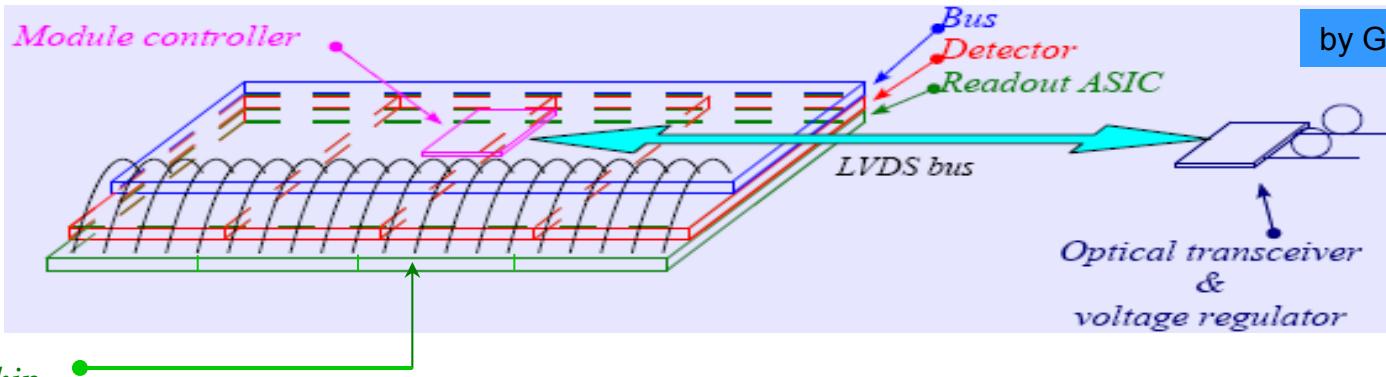


# ASIC prototype

D. Calvo



# First pixel readout prototype

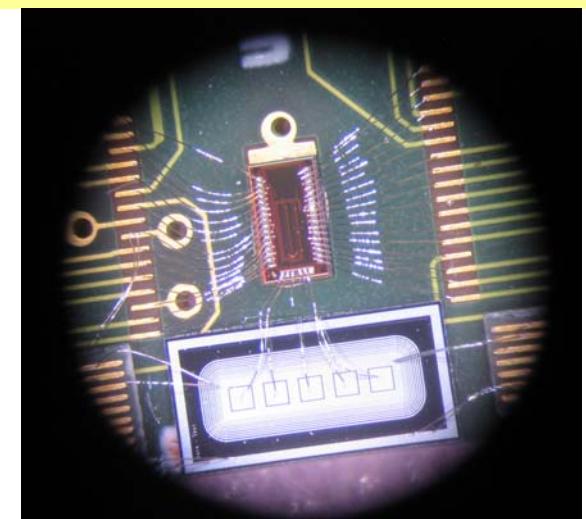


by Gianni Mazza

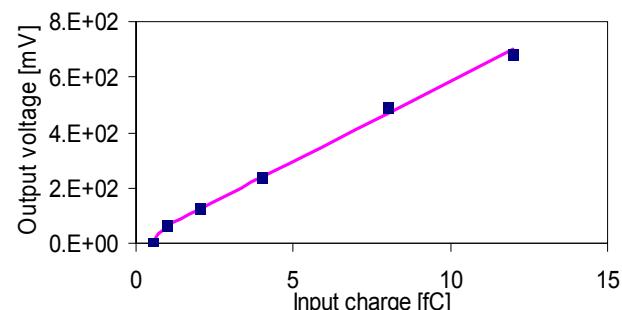
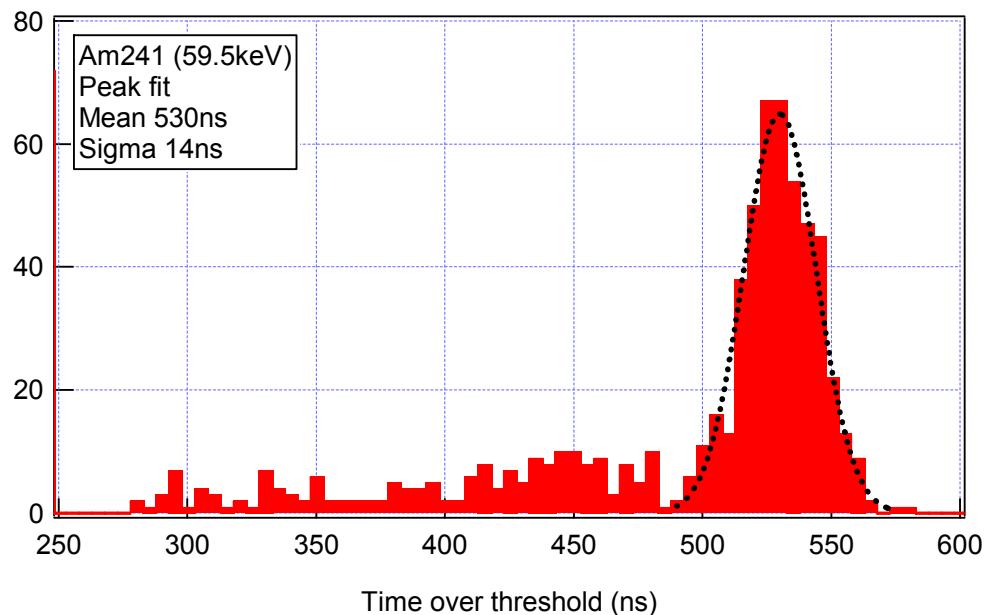
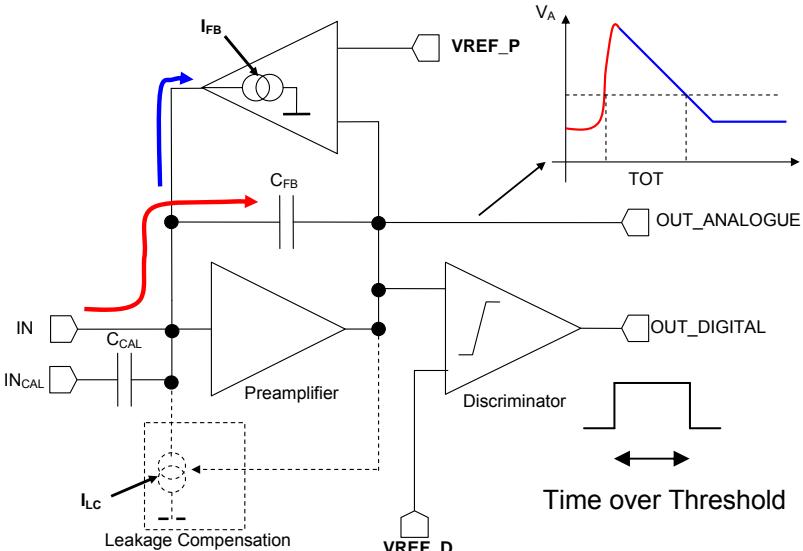
Readout chip

→ **ToPix\_1, CMOS 130 nm technology**

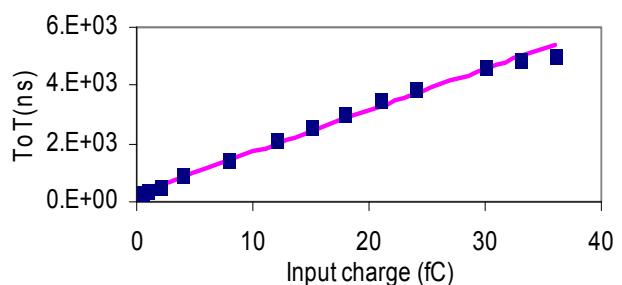
- ✓ 3x2 mm<sup>2</sup> area, 32 cells (8 selectable groups) with pre-amplifier and discriminator
- ✓ no bump bonding pads, but 6 input lines for connecting external sensors
- ✓ analog power consumption below 12 $\mu$ W @1.2V
- ✓ absence of enclosed structures to study the radiation tolerance of the 130nm CMOS technology



# Results from ToPix\_1



The preamplifier saturates at 12 fC, but....



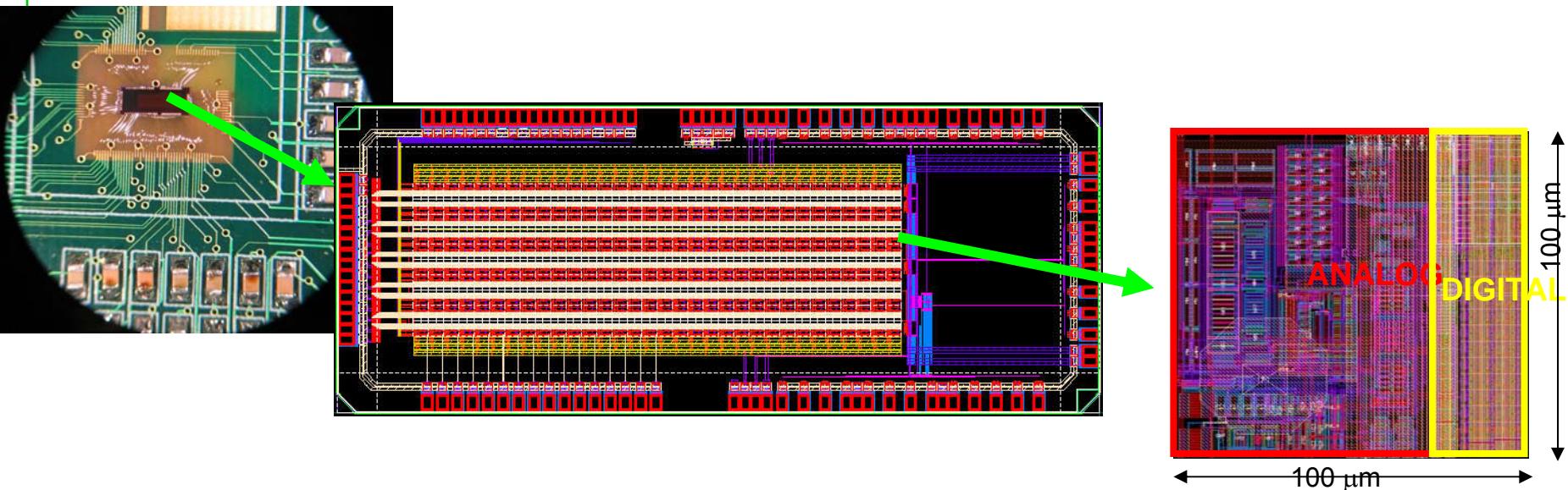
....the ToT preserves good linearity at least up to 40 fC

TID test with X ray sources at CERN and Alessandria University	High dose rate 400 rad/s (20 Mrad)	Low dose rate 1.1 rad/s (3Mrad)
Leakage current max. variation (mean value 3mA)	11 %	8 %
Threshold and baseline max. variation (mean value:300 mV)	11 %	5.5 %
Preamplifier gain relative variation	3 %	1.5 %
ToT gain relative variation	18 %	9 %

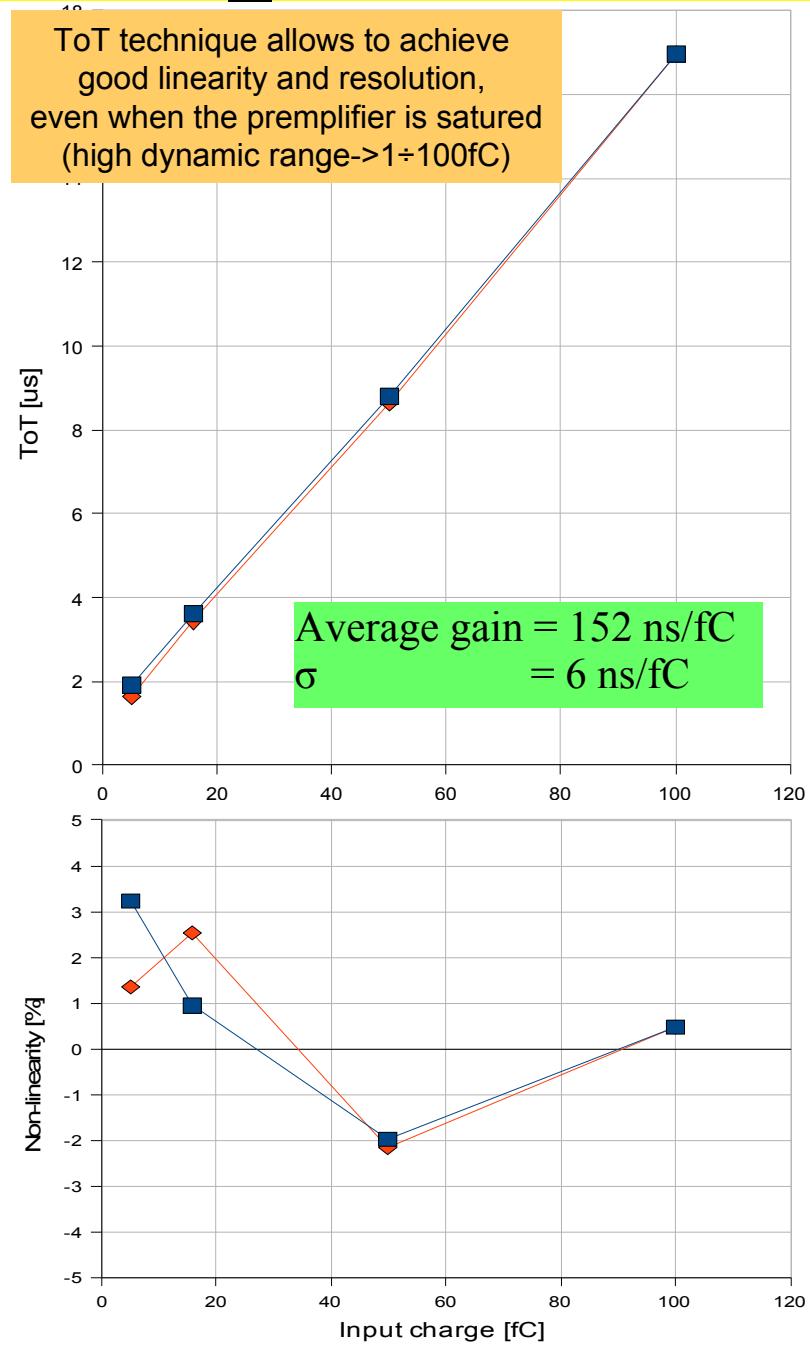
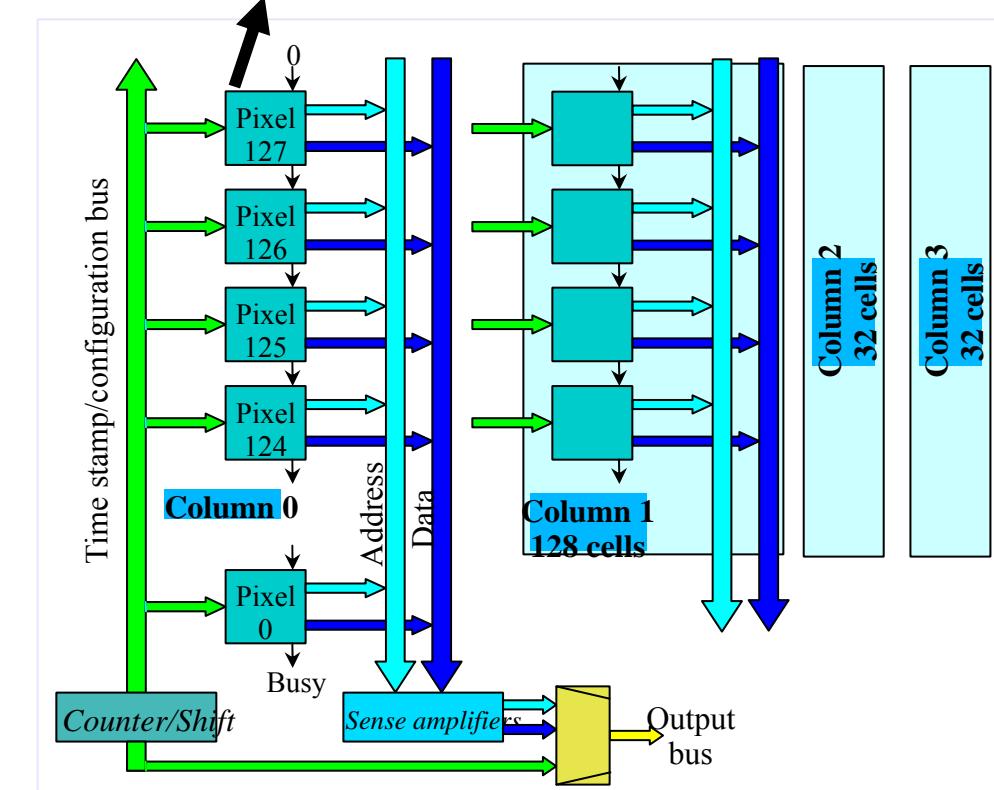
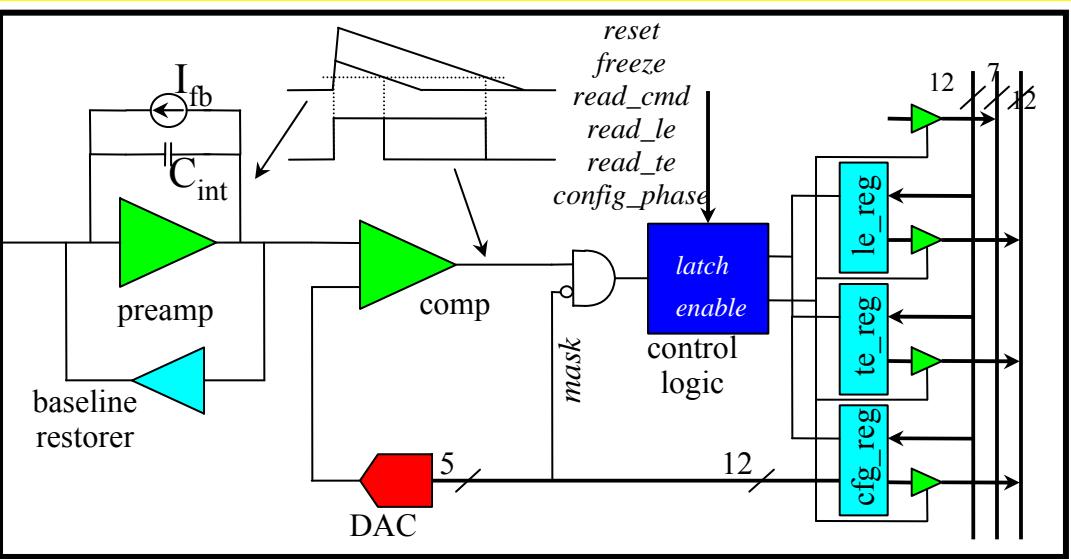
# Second pixel readout prototype

## → ToPix\_2, CMOS 130 nm technology

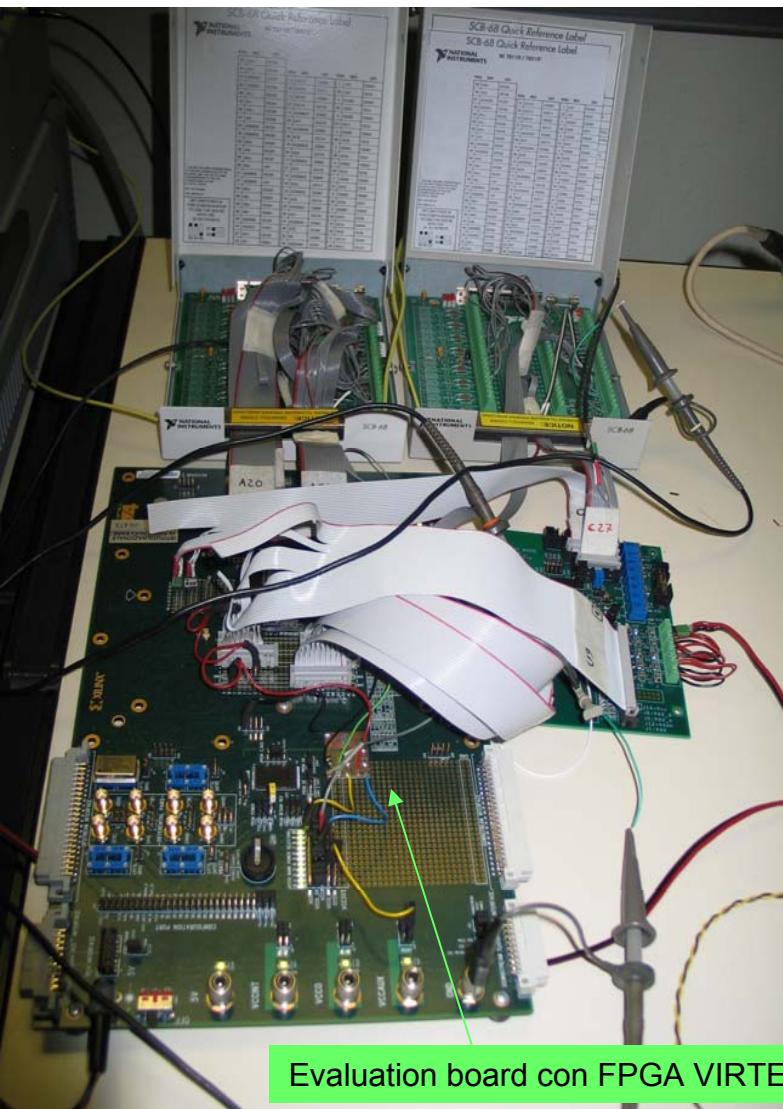
- 5x2 mm<sup>2</sup> area with 4 folded columns with a total of 320 readout cells of 100x100 $\mu\text{m}^2$  size
- analogue + digital circuits (analog power consumption below 12 $\mu\text{W}$  @1.2V)
- Time over Threshold technique implemented to obtain a energy loss measurement
- SEU-hardened memory cells (Dice layout)
- absence of enclosed structures to study the radiation tolerance of the 130nm CMOS technology
- inputs for connecting external sensors
- selectable input polarity
- comparator threshold controlled by DAC (5 bits)
- 12 + 12 bits leading and trailing edge, 12 bits configuration registers
- 12 bits bus for time stamp and 12+7 bits output bus for data + address



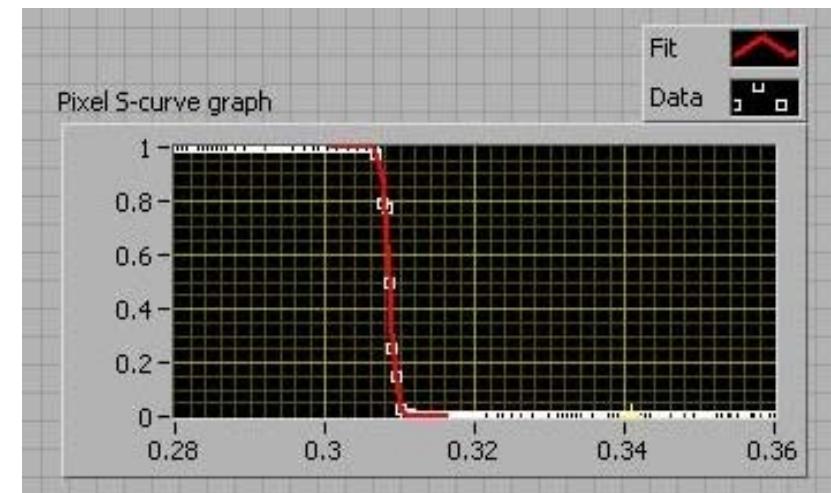
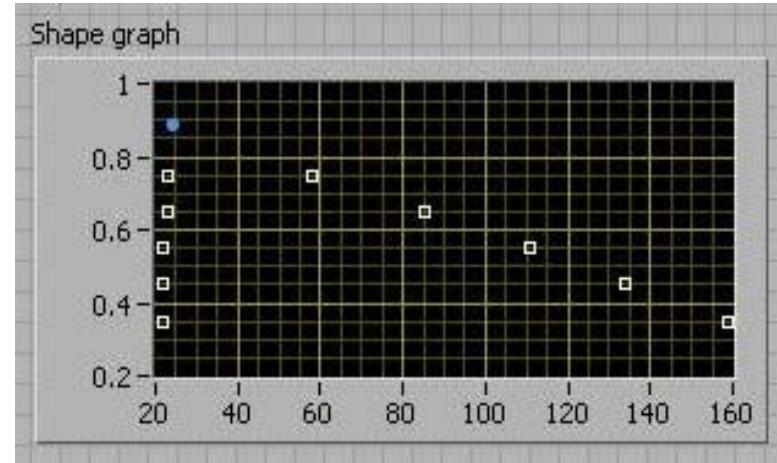
# The architecture of ToPix\_2



# Test station of ToPix\_2



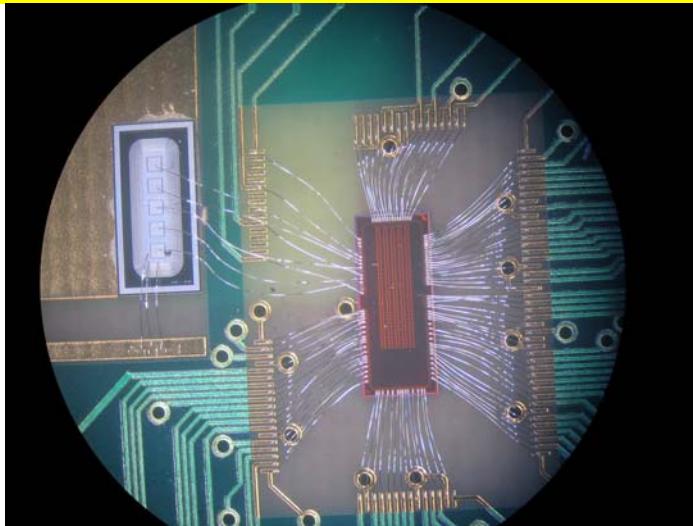
Communication protocol has been verified at 50MHz



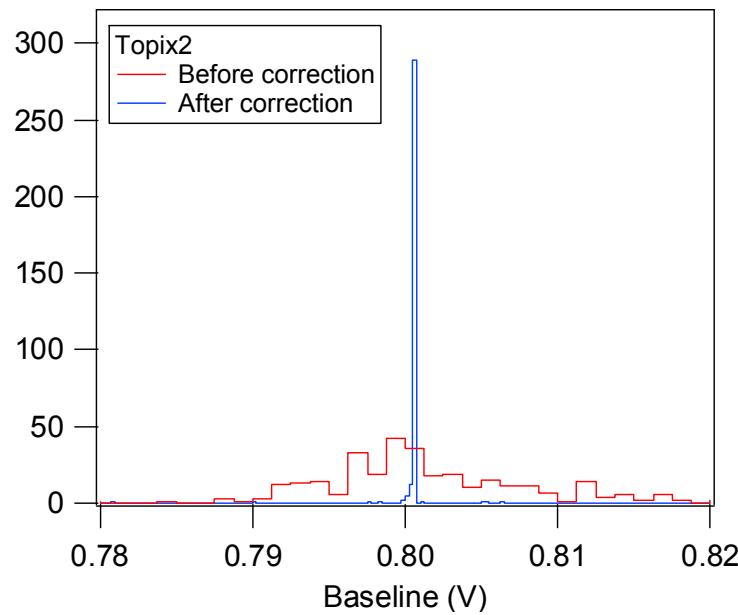
Parameter under test:

The tail slope of the amplifier, which provides the informations on the current generator.  
The S curve of the discriminator, which gives the value of the amplifier baseline.

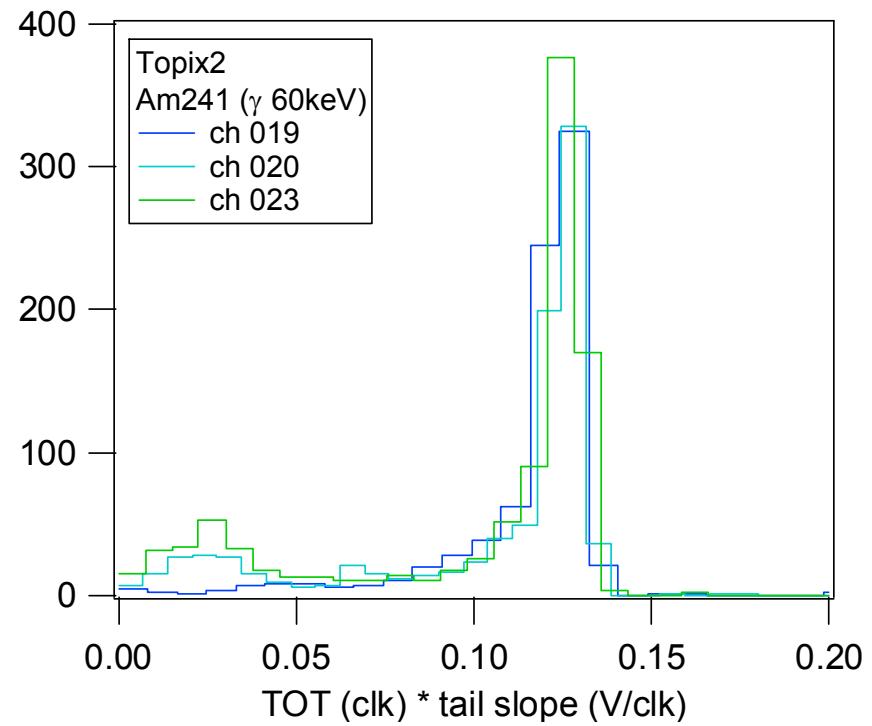
# ToPix\_2 and sensor



- ToPix\_2 - FZ pixel ( $400\mu\text{m} \times 400\mu\text{m}$ ,  $200\mu\text{m}$  thick) connection using wire bonding
- test with gamma rays (60 KeV) from  $^{241}\text{Am}$  radioactive source



Individual pixel DAC baseline correction

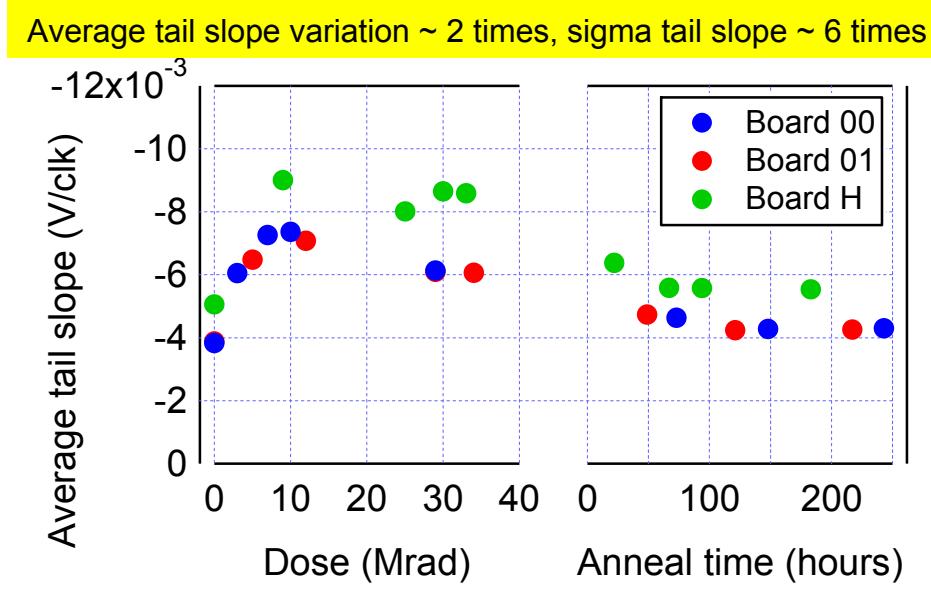
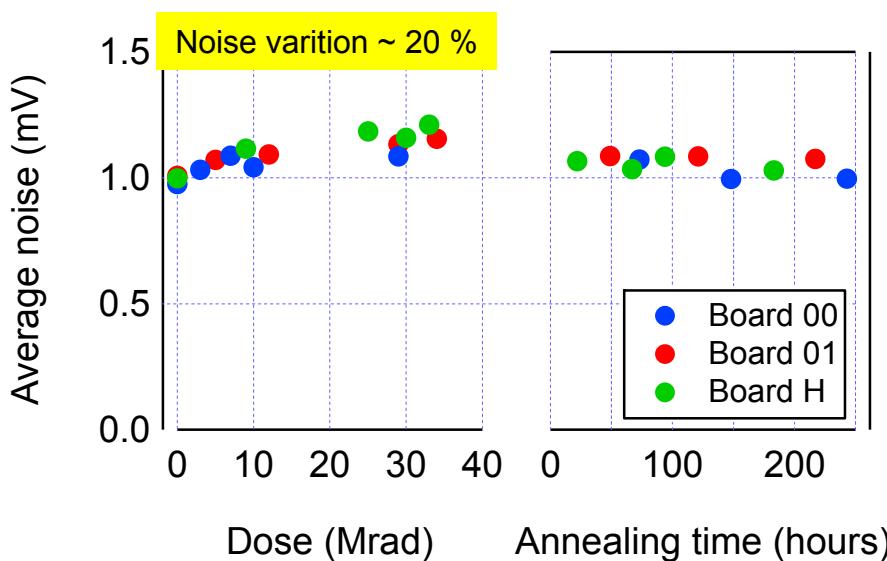
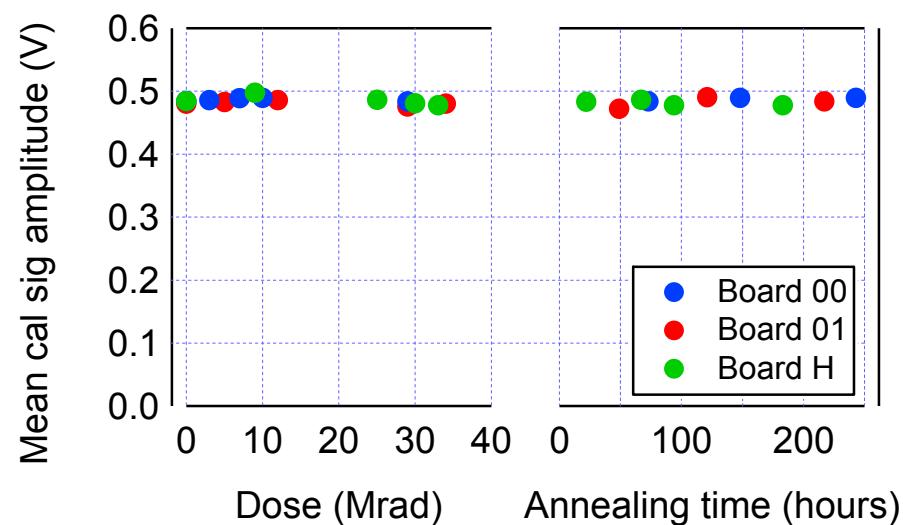
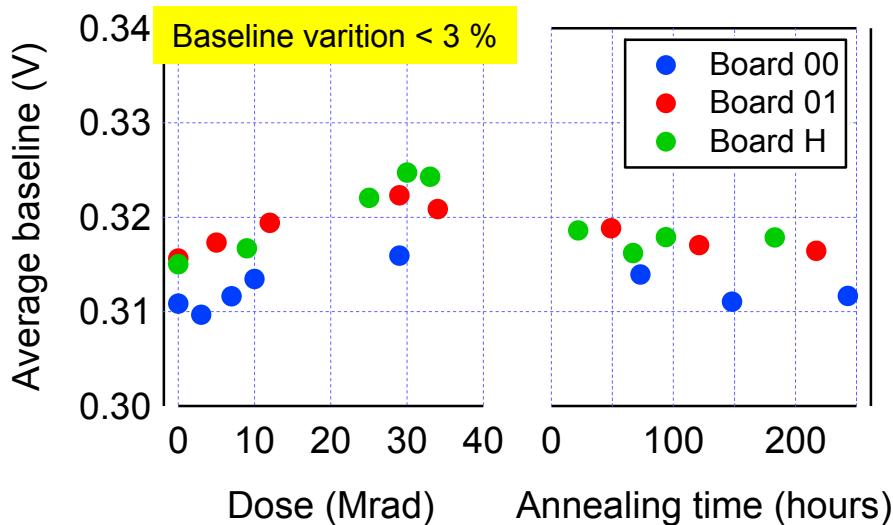


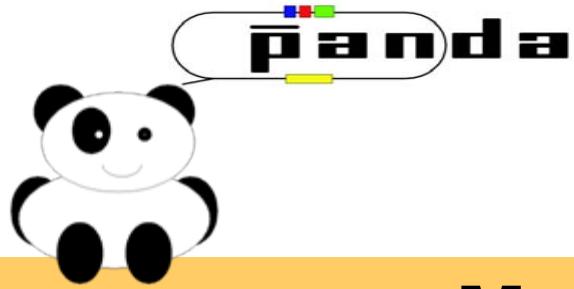
TOT calibration

# TID test on ToPix\_2

Total Ionizing Dose (TID) with X rays for 6 chips:

- 600 rad/s ( $> 30$  MRad final dose) + annealing phase at 25/100 °C (X ray source provided at CERN by Federico Faccio)



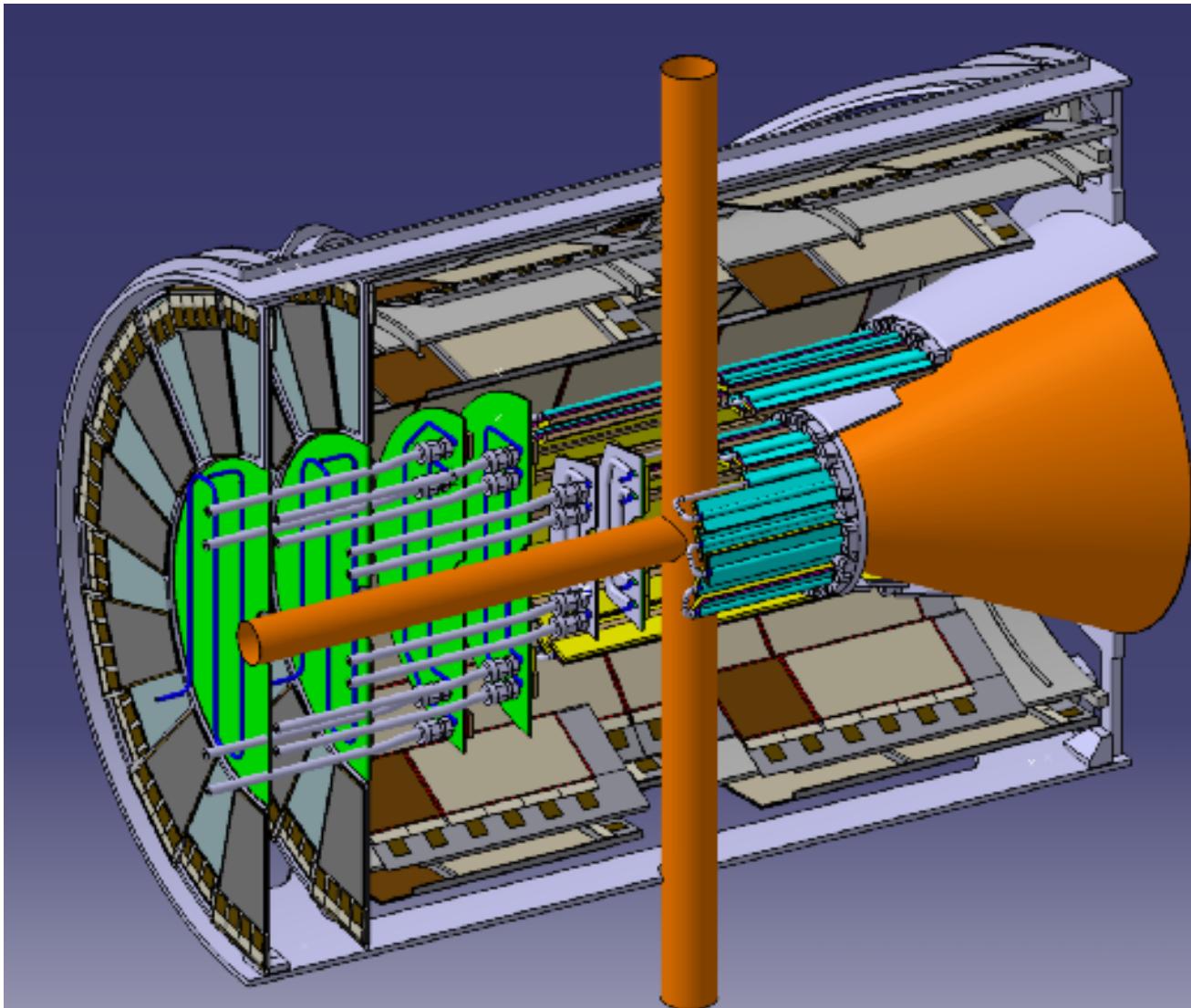


# Mechanics and cooling

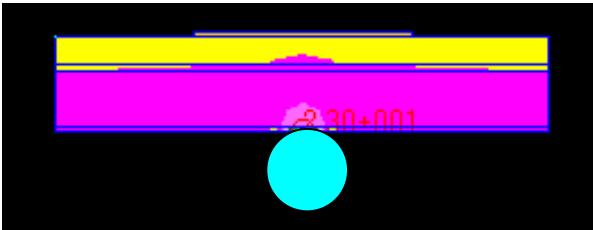
D. Calvo



# Preliminary MVD mechanics and cooling design



# Thermal Simulations of the Test Model



## FIRST TEST MODEL:

Dummy FEE: 0,5 mm Alumina (20 W/mK) + 0,1 mm with Power: 5W

Glue layer: 0,1 mm (Epo-Tek H70, Master Bond EP30AN, Arctic Silver)

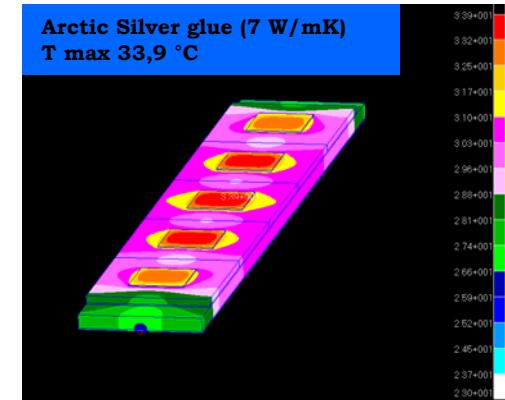
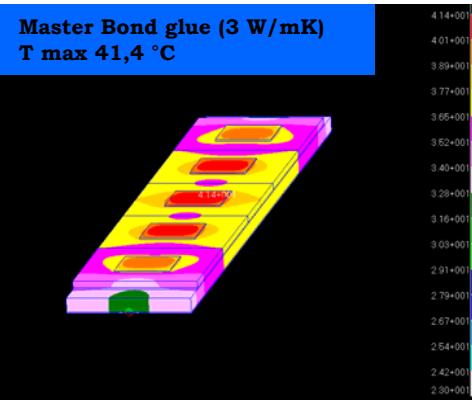
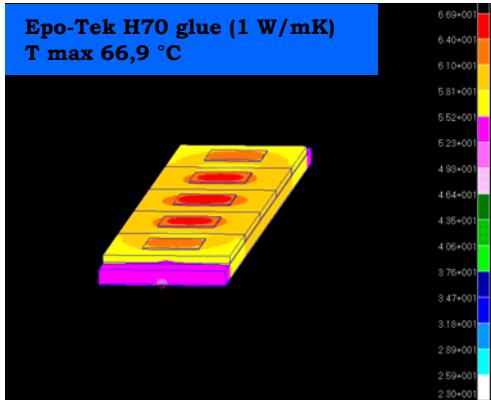
Carbon foam: 1 mm (40 W/mK)

Glue layer: 0,1 mm (Epo-Tek H70, Master Bond EP30AN, Arctic Silver)

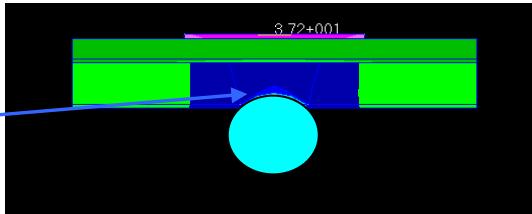
Cooling water 18°C (about 23°C on the wall). Flow rate : 0,3 lit/min

MODEL LENGTH: 50 mm

Different  
Thermal glues



Improving  
contacts

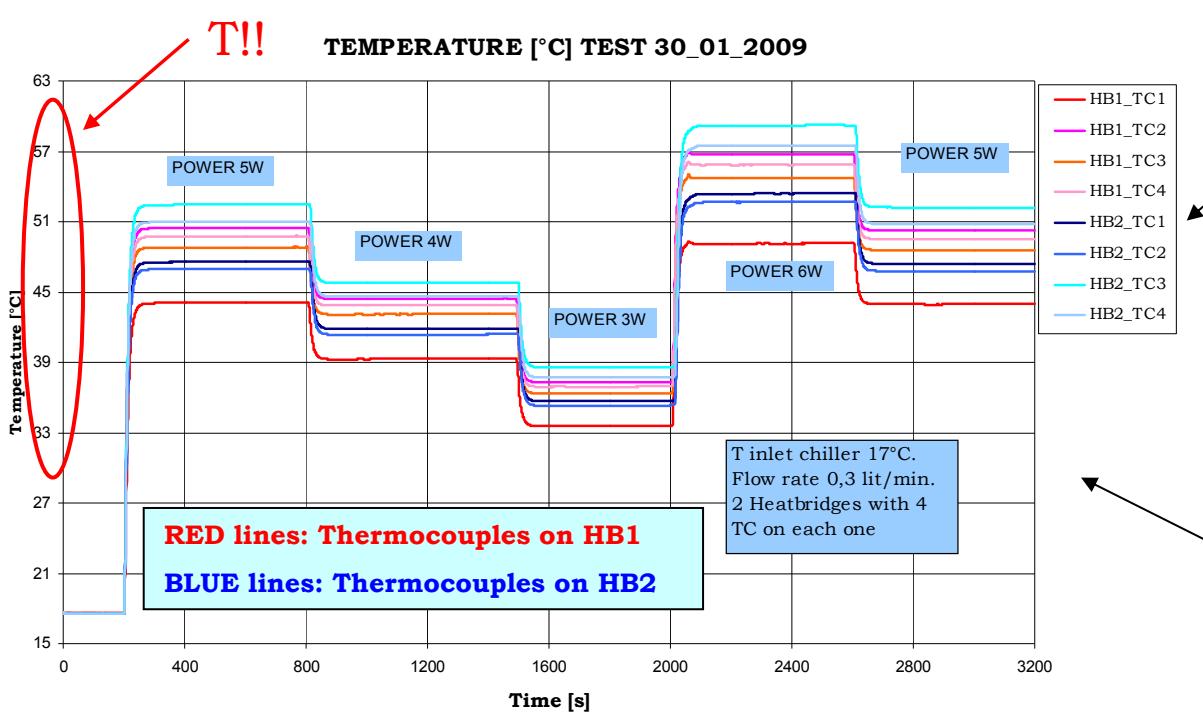


Tube channel  
Epo-Tek H70 glue (1 W/mK)  
T max 37,2 °C

Tube channel  
Master Bond glue (3 W/mK)  
T max 30,4 °C

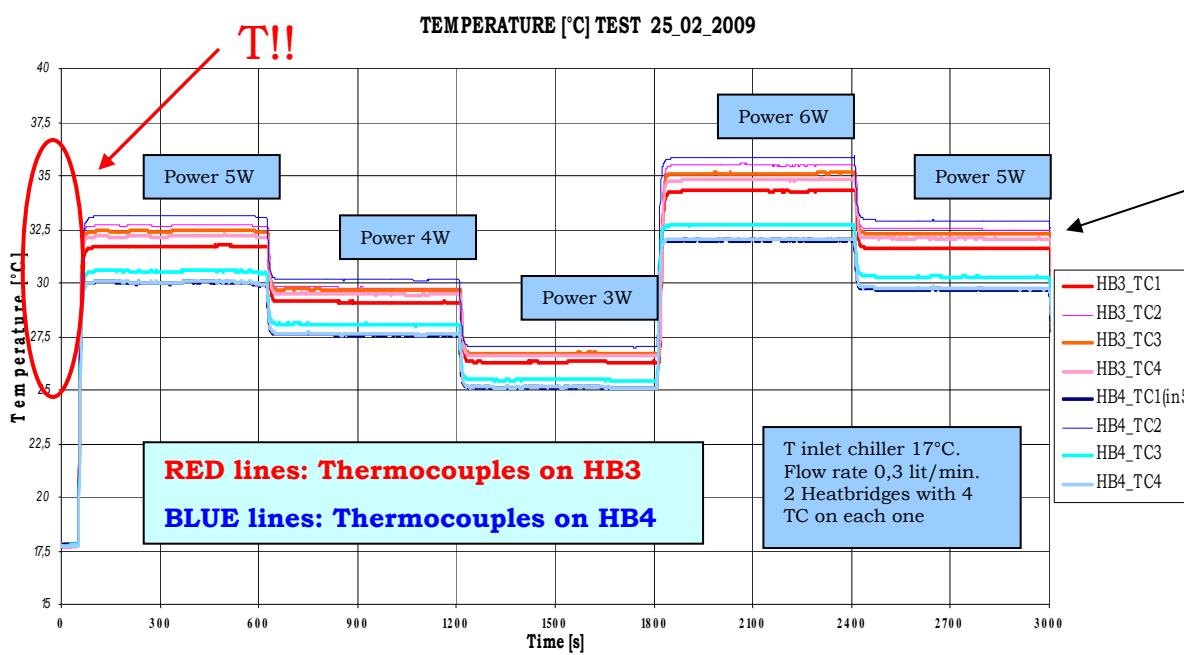
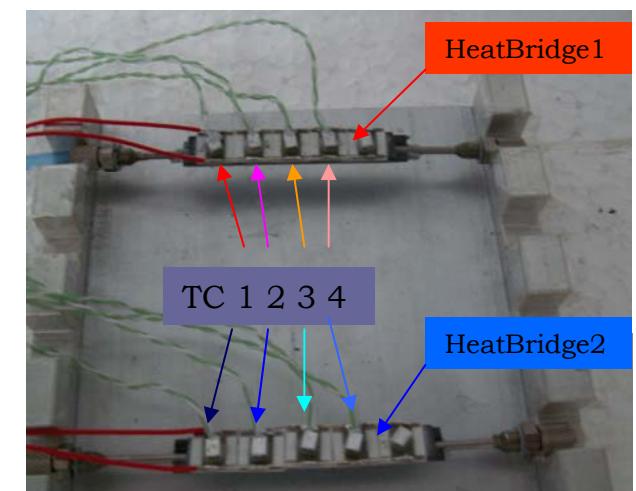
Tube channel  
Arctic Silver glue (7 W/mK)  
T max 28,2 °C

Better contact  
and different  
glues



### TEST RESULTS ON PROTOTYPES GLUED WITH **MASTER BOND**

**HB1** and **HB2**: Omega in carbon fiber; tube in MP35N 2mm O.D. and 1,84 mm I.D.; carbon foam 1 mm; dummy chip in alumina.



### TEST RESULTS ON 2 PROTOTYPES GLUED WITH **ARTIC SILVER**

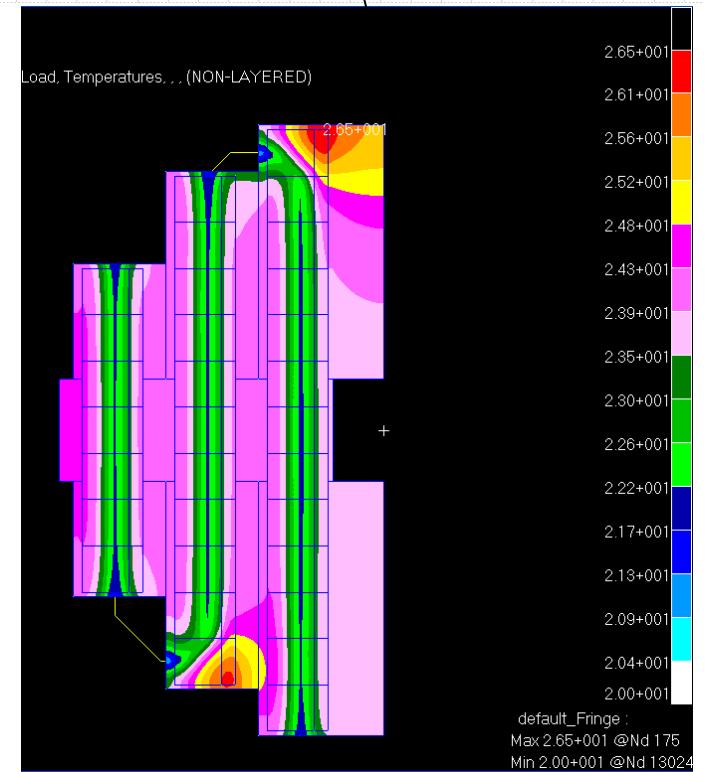
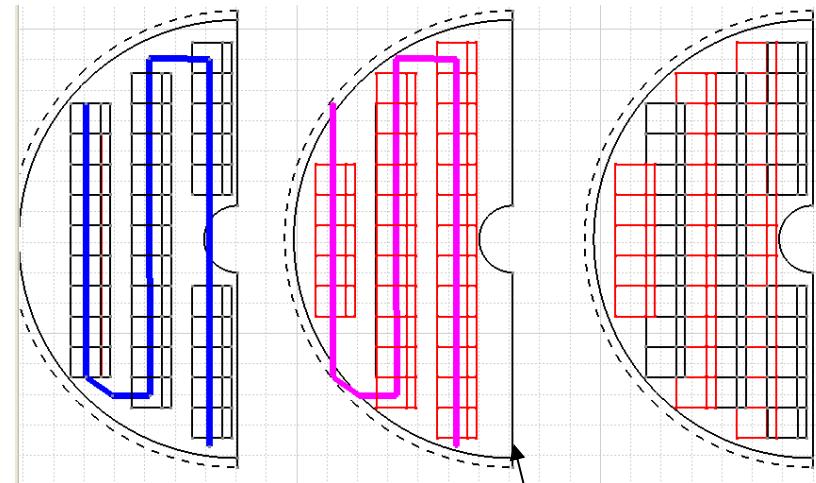
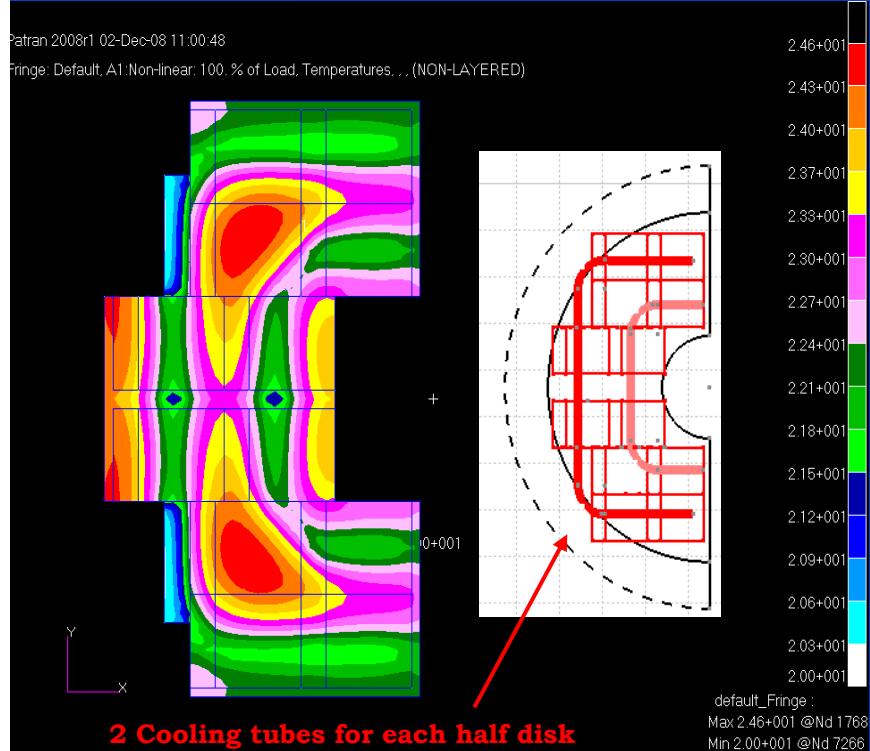
**HB3**: Omega in carbon fiber; tube in MP35N 2mm O.D. and 1,84 mm I.D.; carbon foam 1 mm; dummy chip in alumina. Problem with dummy chip2: probably damaged (HB3\_TC2 instable).

**HB4**: Omega in carbon fiber; tube in MP35N 2mm O.D. and 1,84 mm I.D.; carbon foam 1 mm; tube contact improved; dummy chip in alumina. Problems with welds in dummy chip 1 and 2 (HB4\_TC2 higher T respect blue TC1(in5), TC2, or TC3).

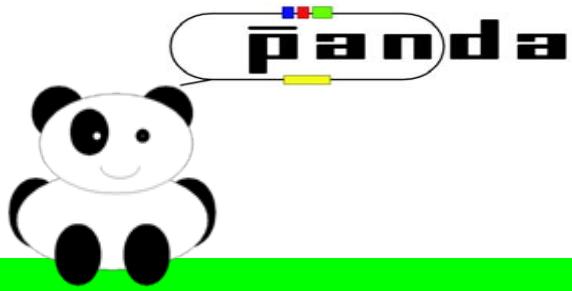
# Disk cooling studies

Patran 2008r1 02-Dec-08 11:00:48

Fringe: Default, A1:Non-linear, 100. % of Load, Temperatures, ... (NON-LAYERED)

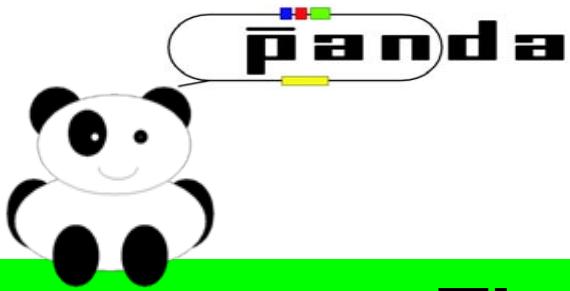


D. Calvo



# Conclusion

- FAIR is the future european facility for antiproton and ions research
- PANDA design is in progress and first detector prototypes have been made
- Simulation work in progress to optimize the MVD design
- New ASIC prototype under study for the pixel readout
- Further tests on sensors for the pixel detector



# Thanks to MVD people !

MVD Group:

- HISKP, Universitat Bonn, Germany
- INFN – Sezione di Torino
- IKP, Forschungszentrum Julich, Germany
- IKTP, TU Dresden, Germany
- Universita' di Torino – Fisica Sperimentale
- FBK di Trento

<http://www.gsi.de/>

[http://www-panda.gsi.de/auto/\\_home.htm](http://www-panda.gsi.de/auto/_home.htm)

<http://panda-wiki.gsi.de/cgi-bin/view/Mvd/MvdPublic>